

Principles of Micro- and Nanofabrication for Electronic and Photonic Devices

Materials: Structures and Synthesis

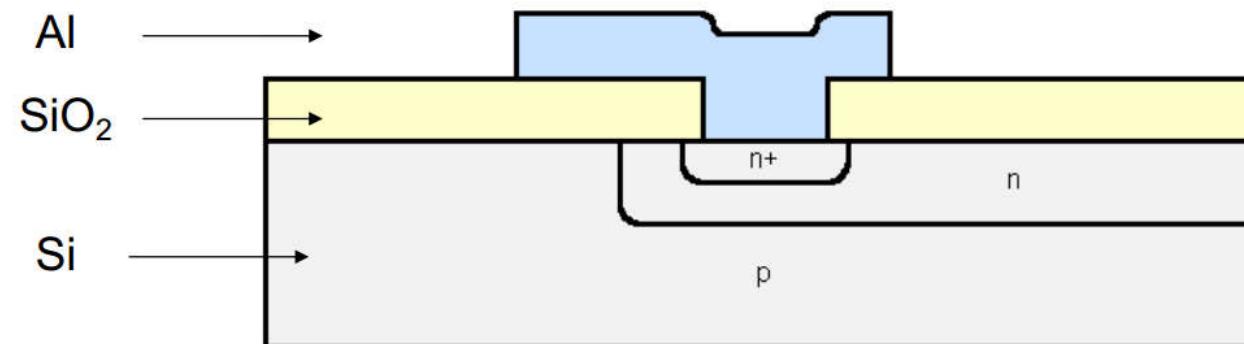
Xing Sheng 盛 兴



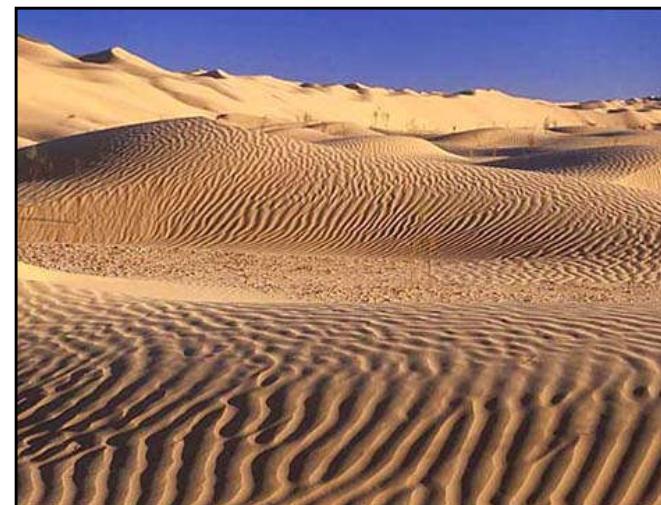
Department of Electronic Engineering
Tsinghua University
xingsheng@tsinghua.edu.cn

Raw Materials

MOS: Metal-Oxide-Semiconductor



Silicon



SiO_2

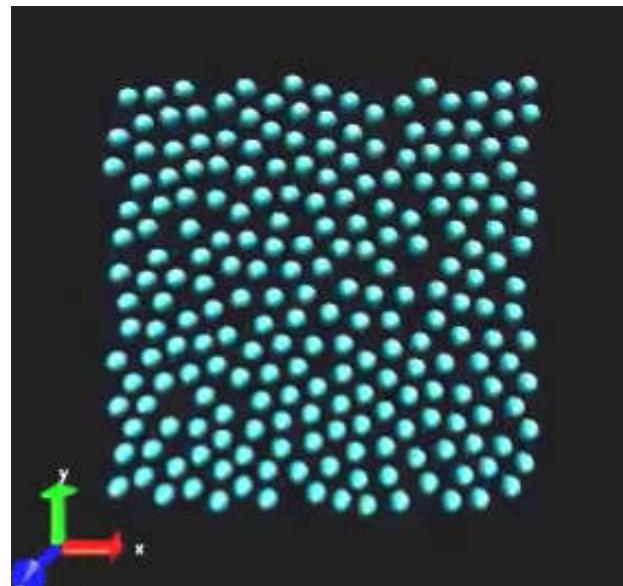
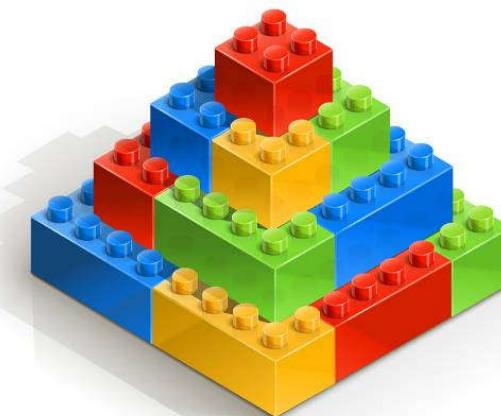


Metal

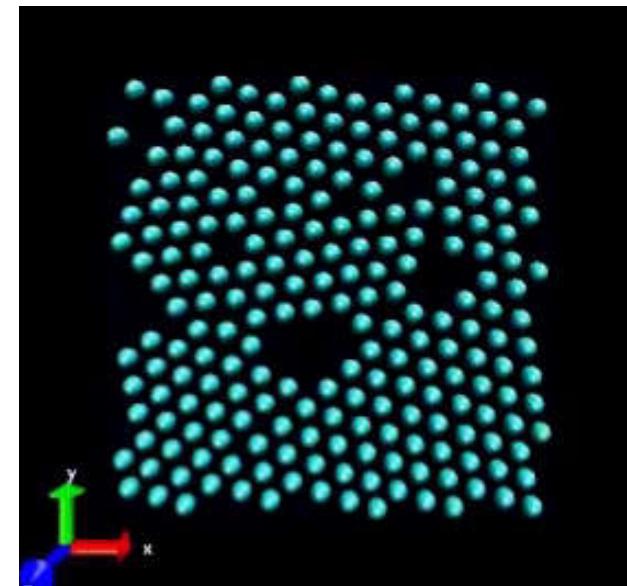
Crystal Structures



?



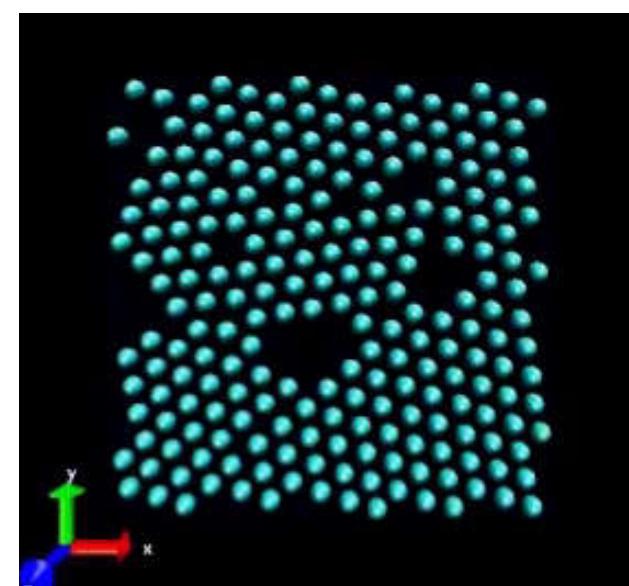
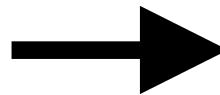
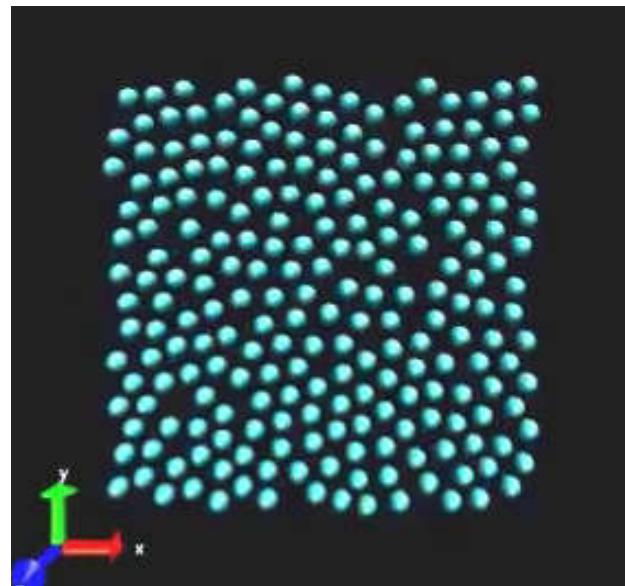
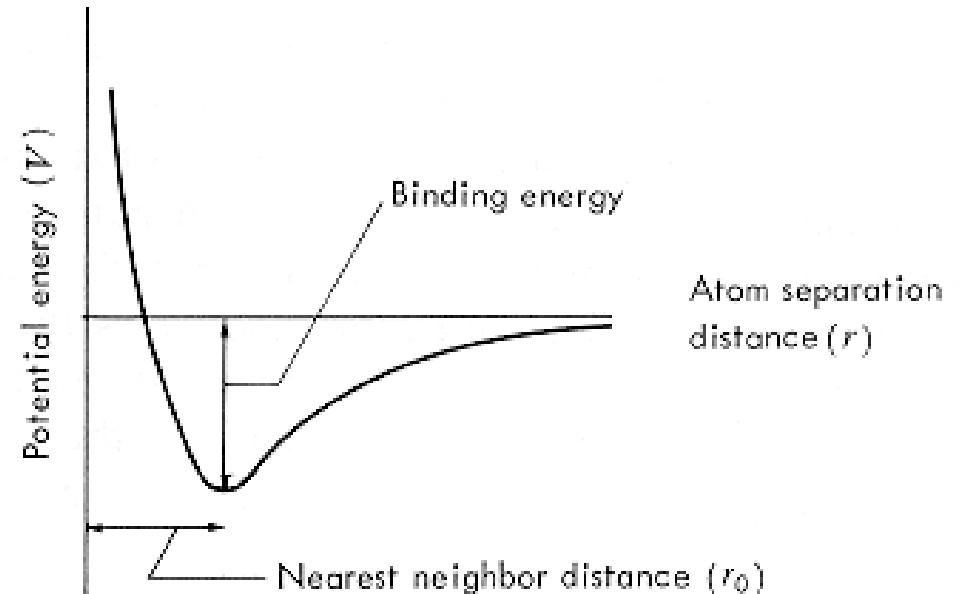
→
Video



It is all about *energy*

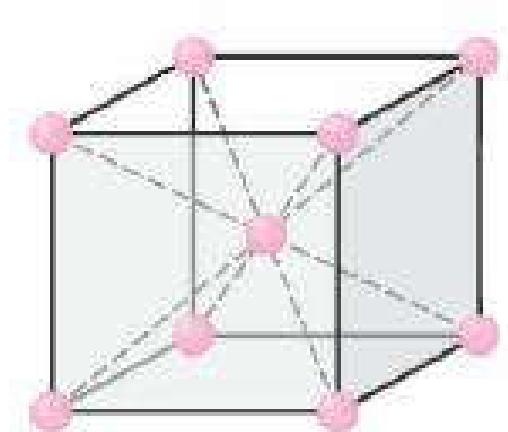
Lennard-Jones Potential

$$V(r) = \frac{A}{r^{12}} - \frac{B}{r^6}$$



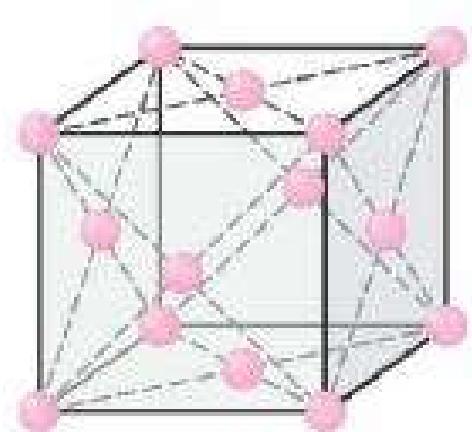
Crystal Structures

Li, Na, Cr,...



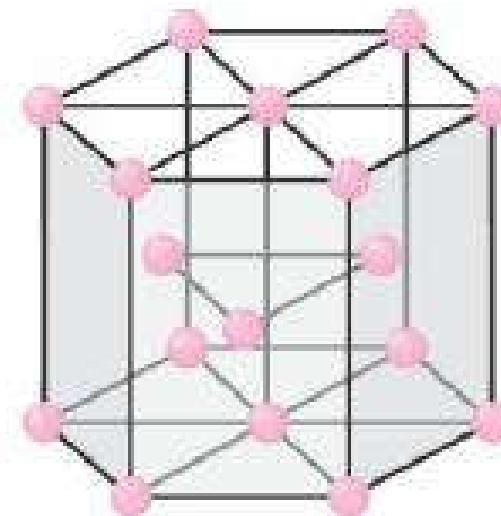
BCC

Al, Cu, Au,...



FCC

Mg, Zn, Ti,...



HCP

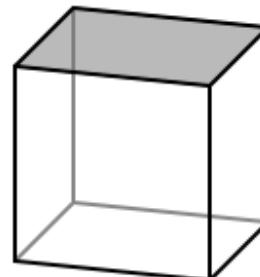
- 3D:
 - 14 Bravais lattices
 - 32 point groups
 - 230 space groups

Miller Indices

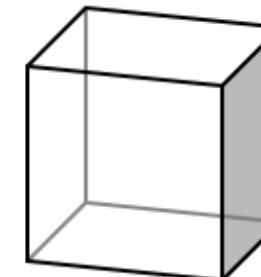
(lmn) plane

intercepts at

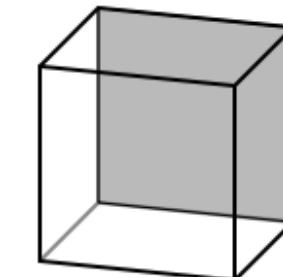
$a_1/l, a_2/m, a_3/n$



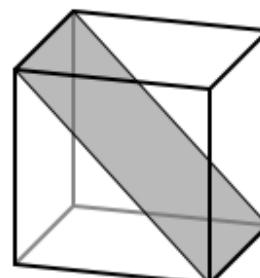
(001)



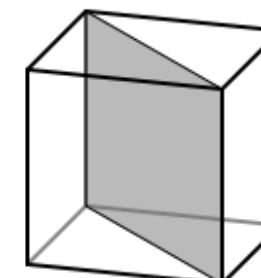
(100)



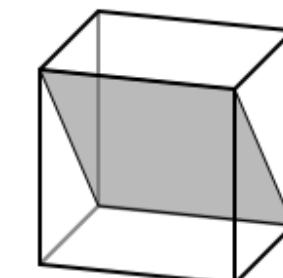
(010)



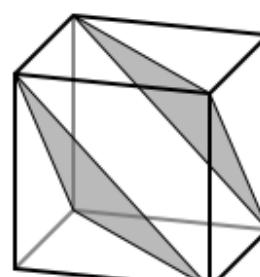
(101)



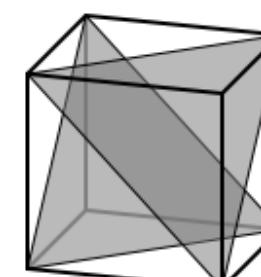
(110)



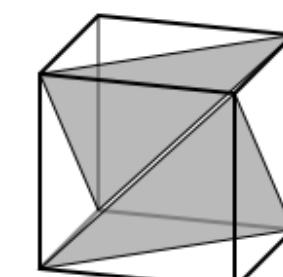
(011)



(111)

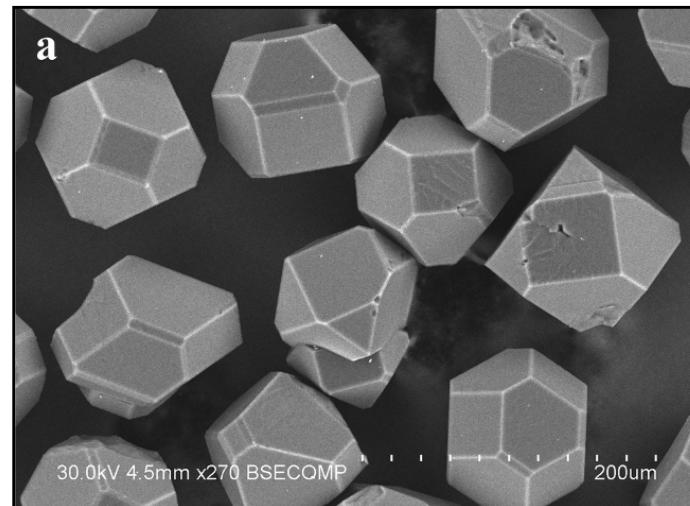
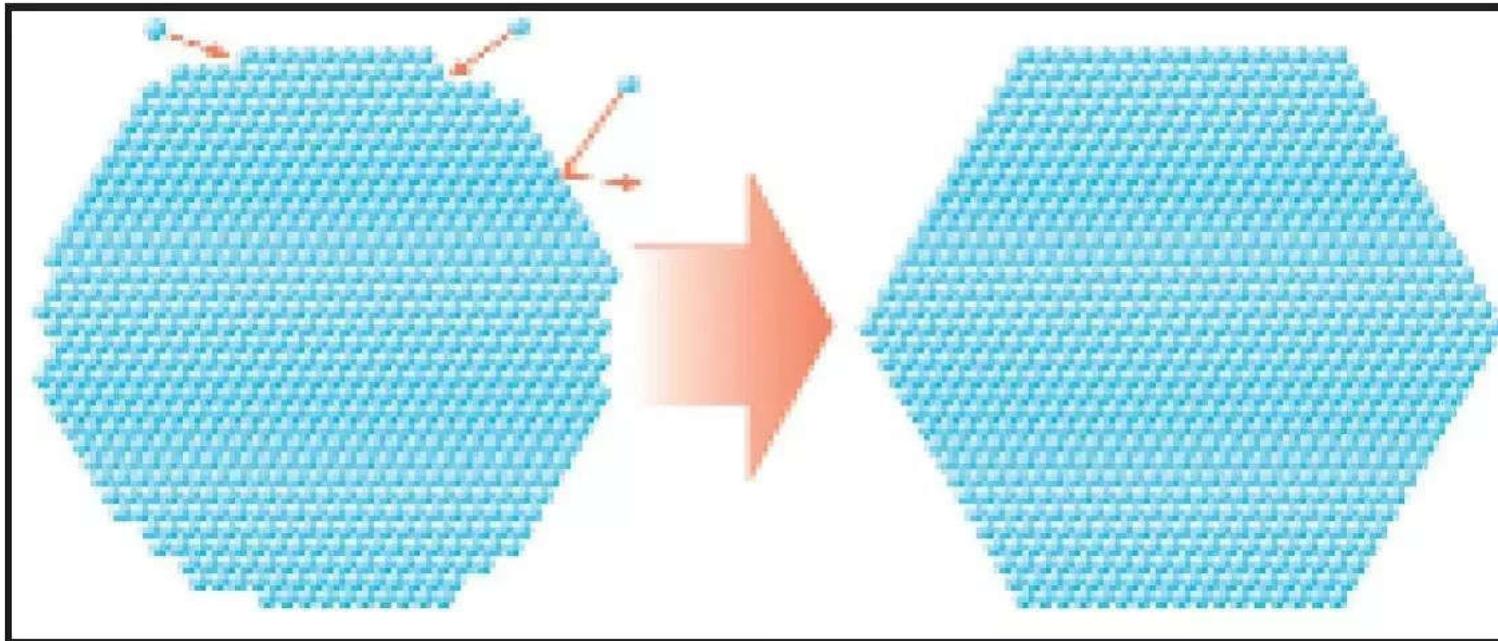


(1-11)



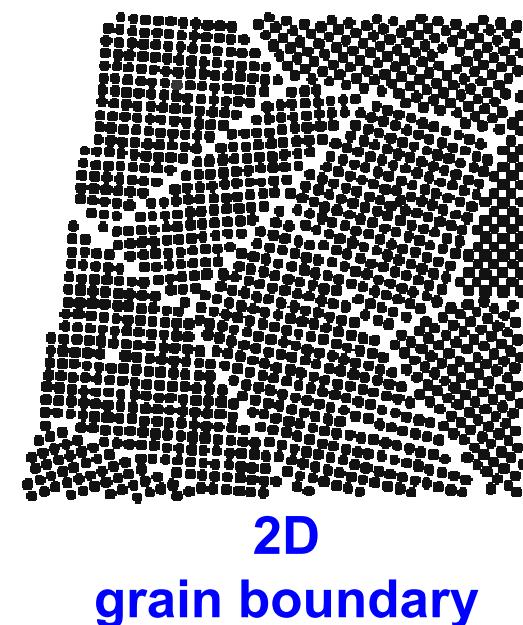
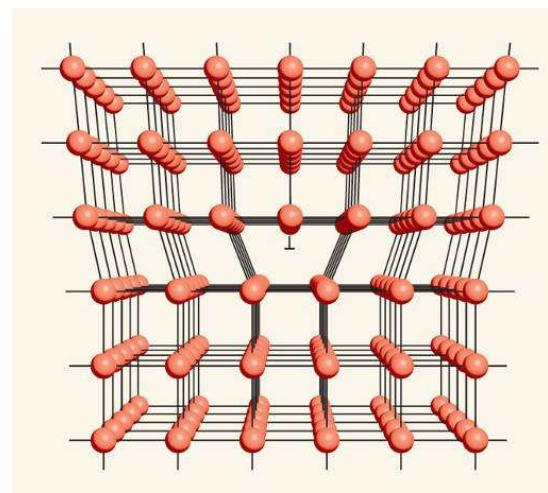
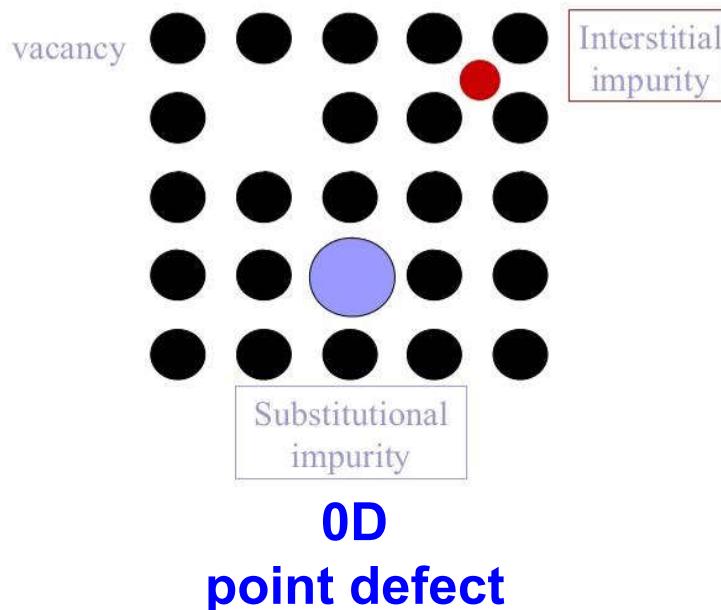
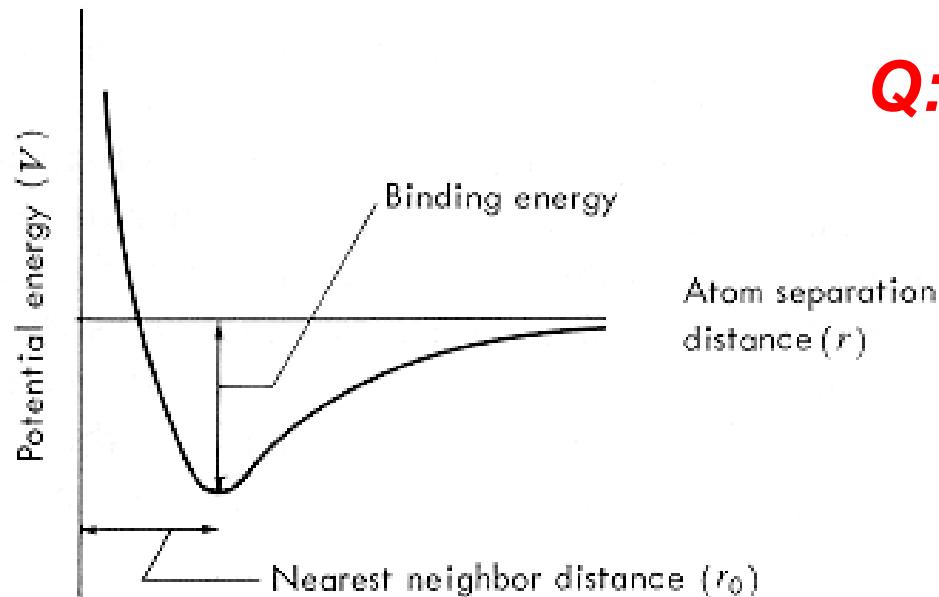
(-111)

Crystals

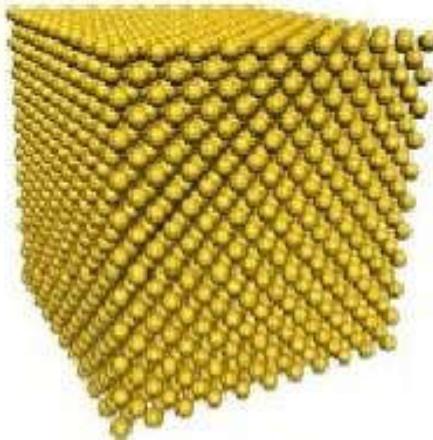


Defects in Crystals

Q: why?



Single Crystal (Mono Crystal)



Quartz

Sugar



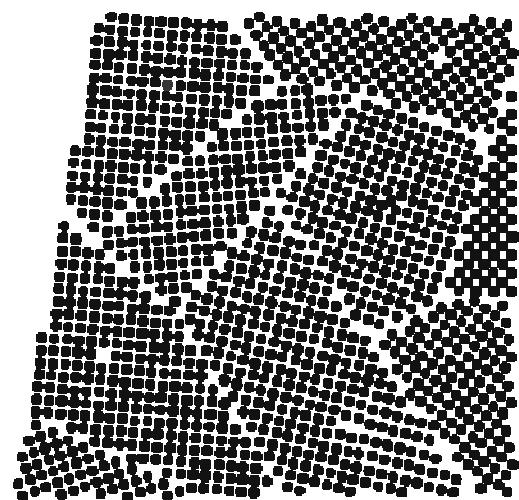
Silicon wafers,
GaAs, GaN, sapphire, ...



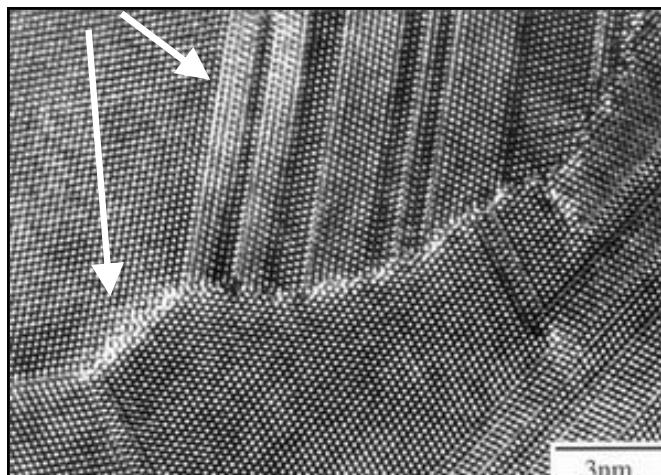
turbine blade



Polycrystal



grain boundary



polycrystalline silicon



Poly-Crystalline
Solar Cell



Mono-Crystalline
Solar Cell



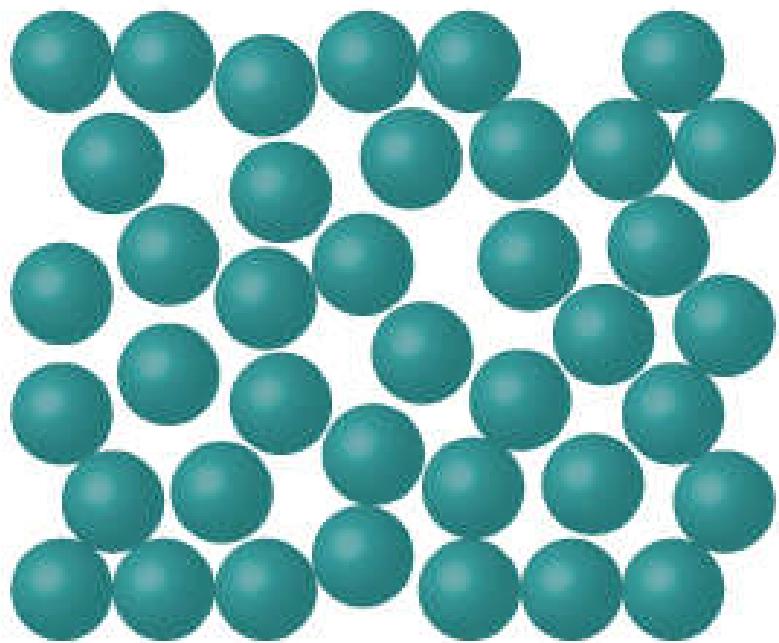
metals



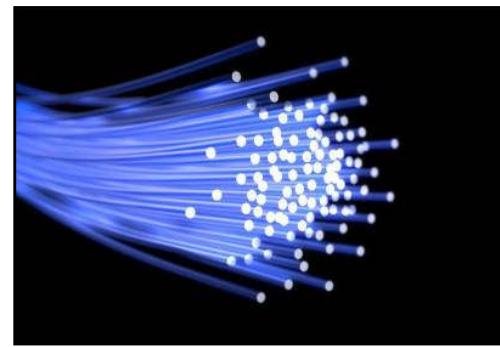
ceramics

Amorphous Materials

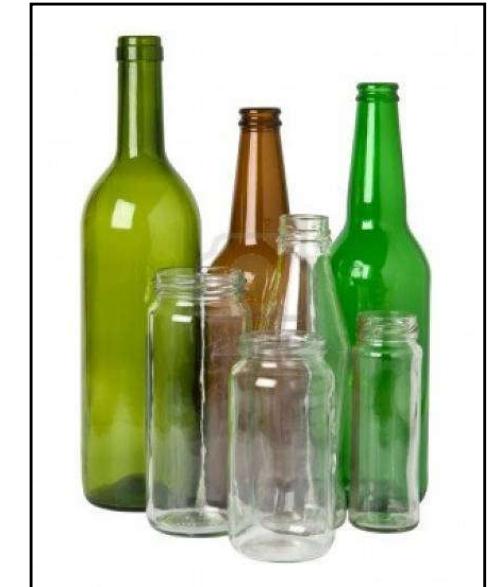
- Defects are everywhere ...



Amorphous



silica fiber



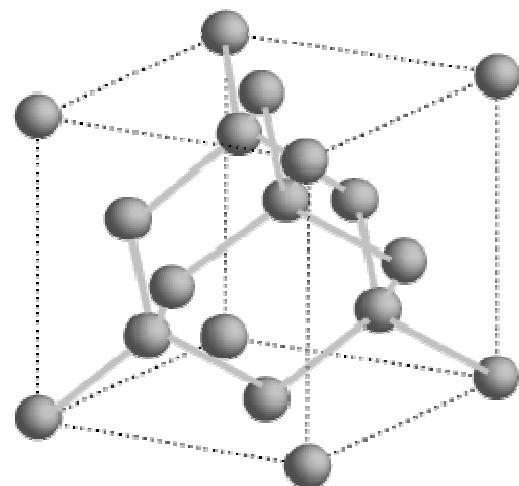
glass



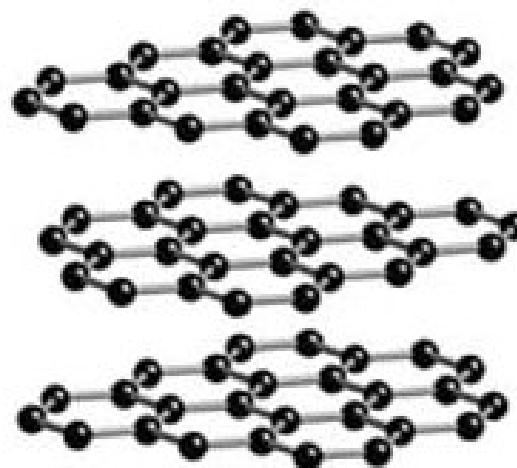
plastics

Q: why is glass transparent?

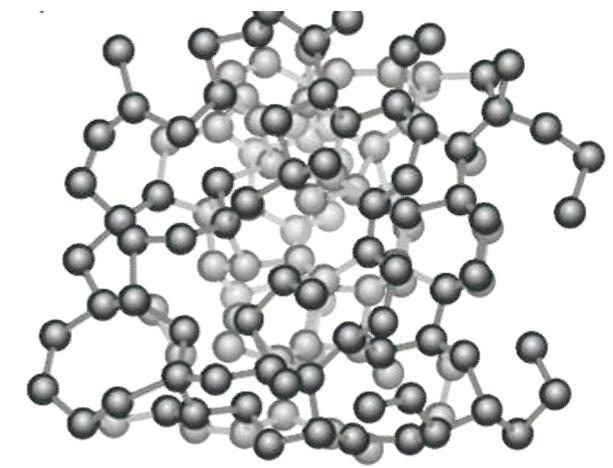
Carbon



diamond



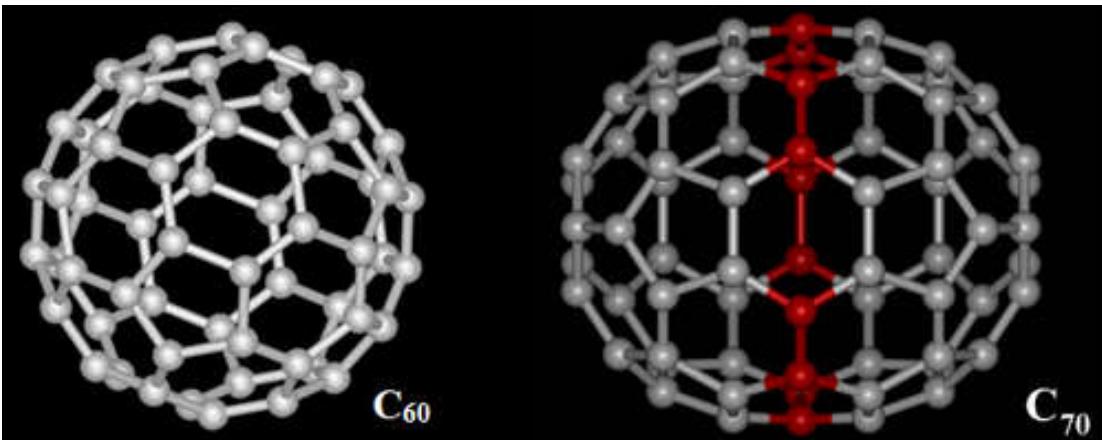
graphite



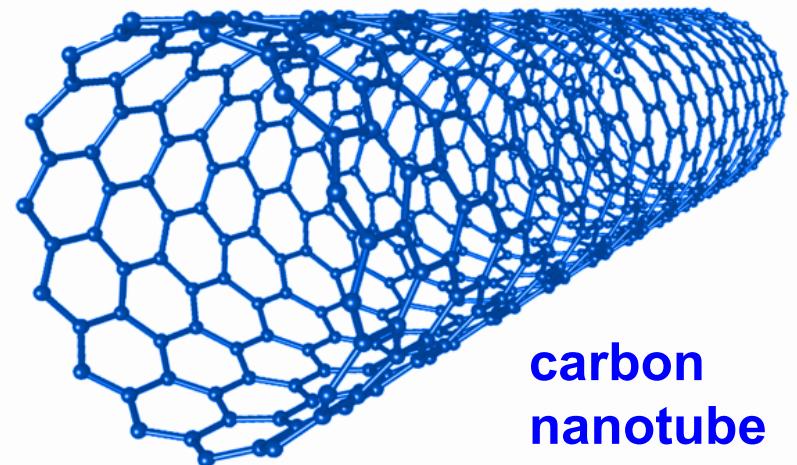
amorphous
carbon

Q: which one is electrically conductive, diamond or graphite?

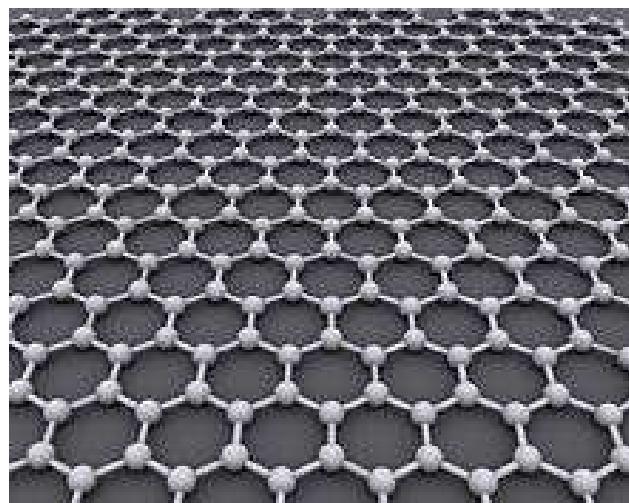
Carbon



H. Kroto, R. Curl, R. Smalley
1996 Nobel Prize in Chemistry



S. Iijima, *Nature* 354, 56 (1991)

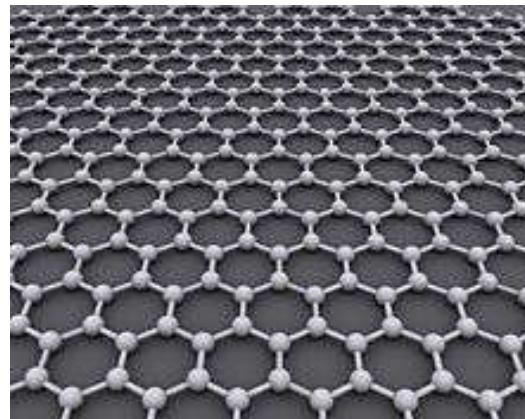


graphene

A. Geim, K. Novoselov
2010 Nobel Prize in Physics

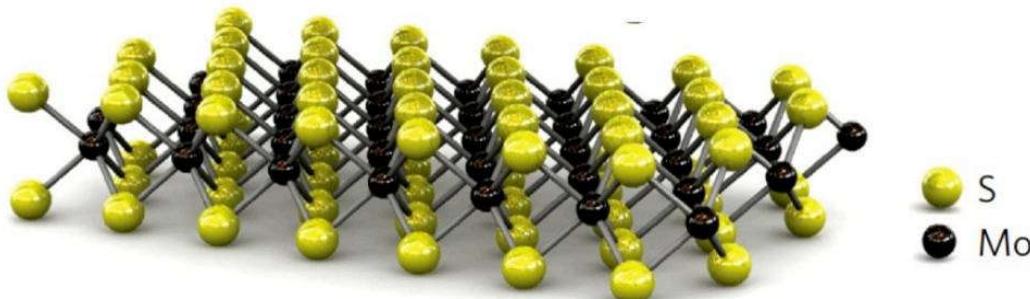
2D Materials

- Single atomic layer crystal

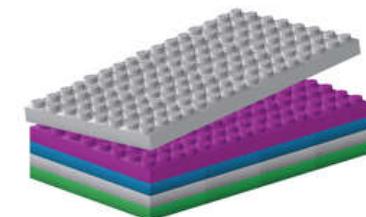
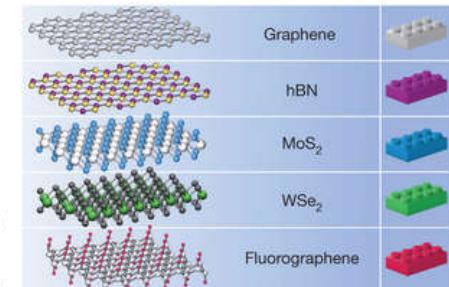
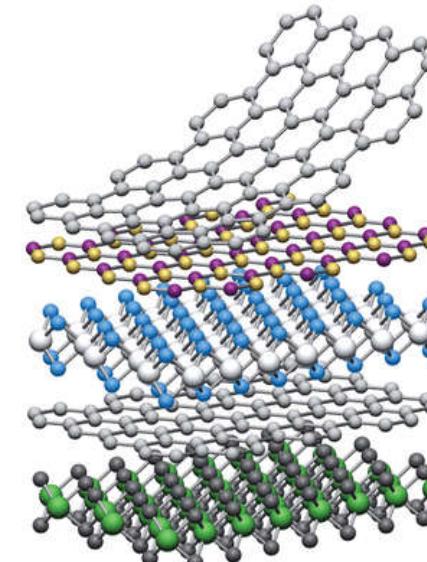


graphene

A. Geim, K. Novoselov
2010 Nobel Prize in Physics

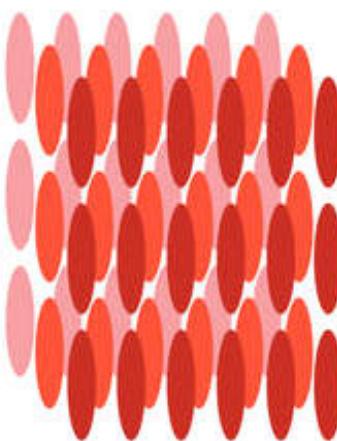


Transition metal dichalcogenide (TMDC)
 MoS_2 , WSe_2 , ...



Liquid Crystals

Crystalline Solid



Liquid Crystal



Isotropic Liquid



Liquid crystal display (LCD)

P. de Gennes
1991 Nobel Prize in Physics

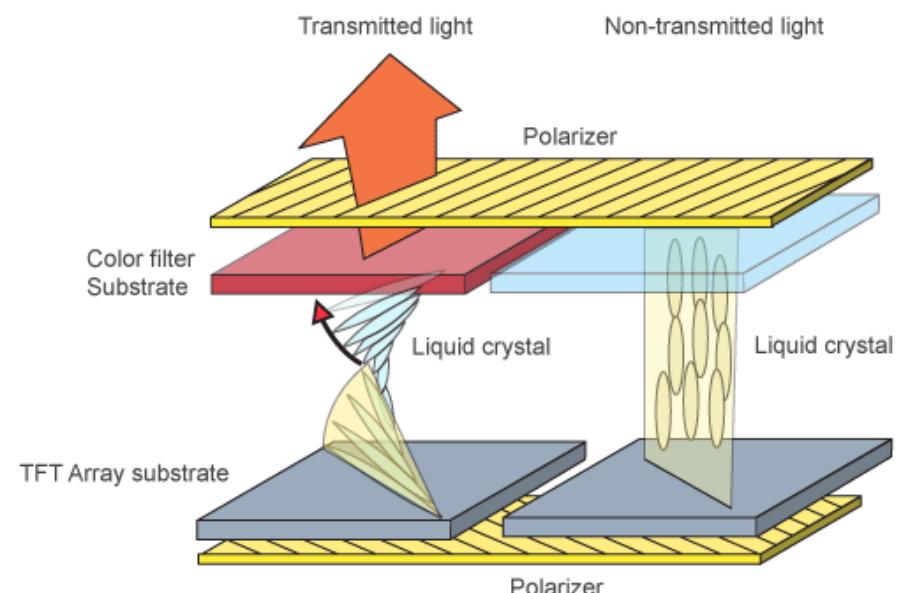
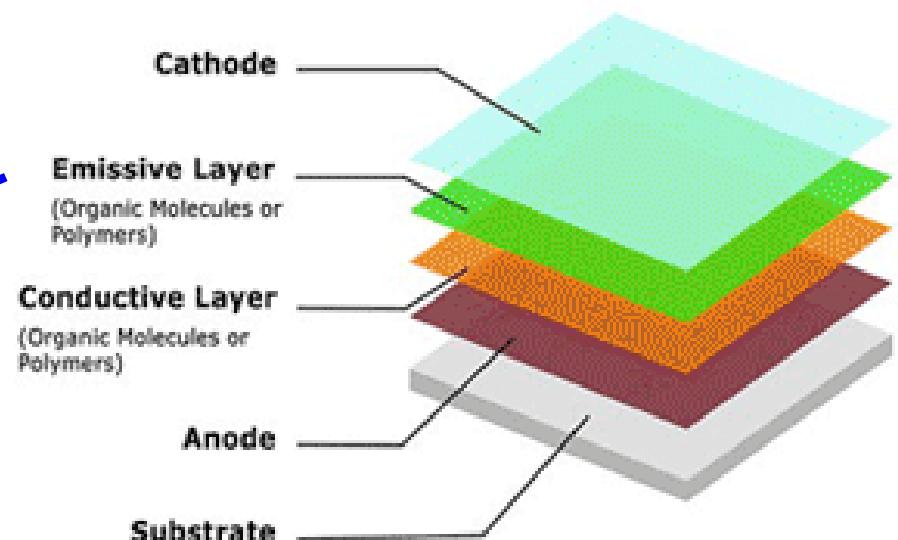
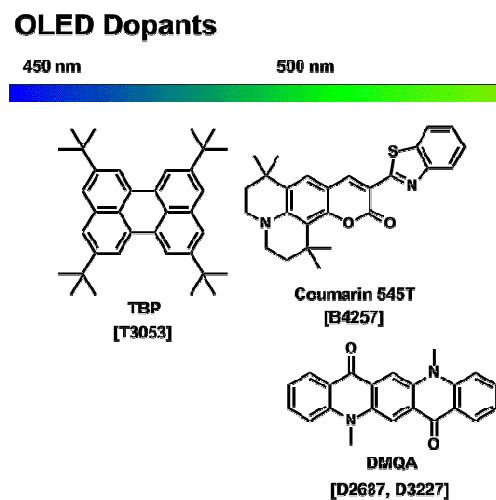


Diagram 2: The Fundamental Photonics of Liquid Crystal (Twisted Nematics)

Organic Materials

■ Small Molecules



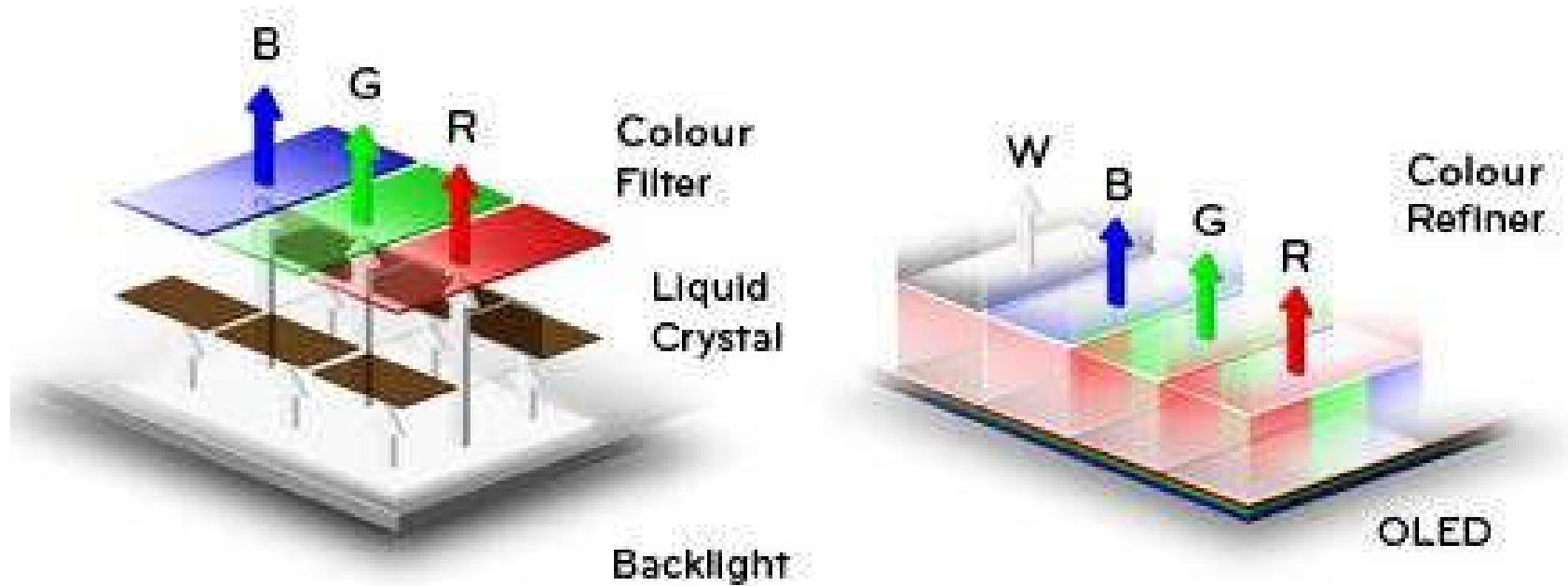
OLED

Organic Materials

LCD

vs.

OLED

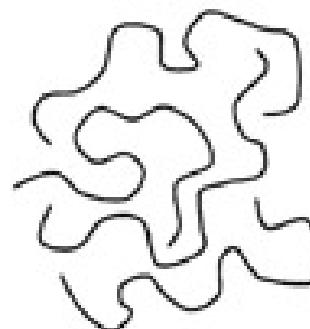
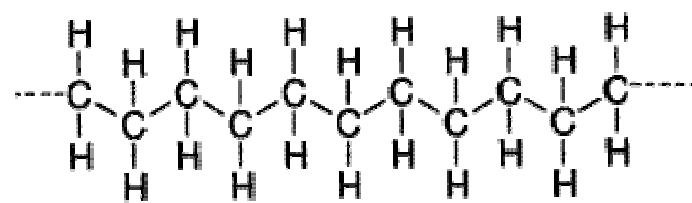


- Complex Structure
- BLU (Backlight Unit) CCFL, LED
- Lighting Unit = Pixel Unit

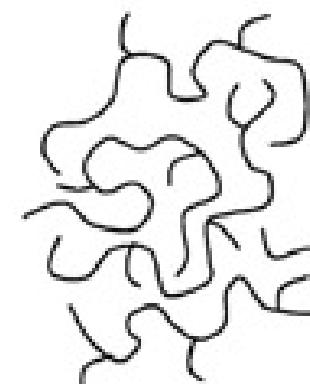
- Simple Structure
- Self-emissive
- Lighting Unit = Pixel Unit

Organic Materials

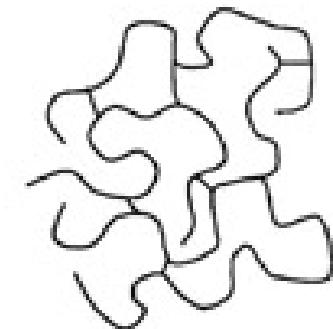
■ Polymers



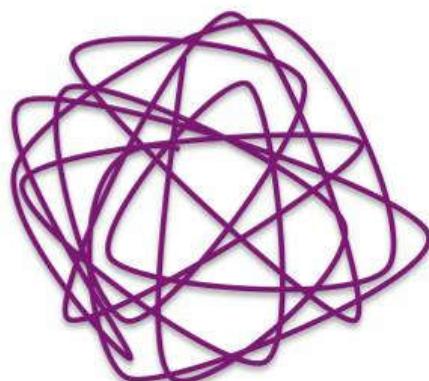
Linear



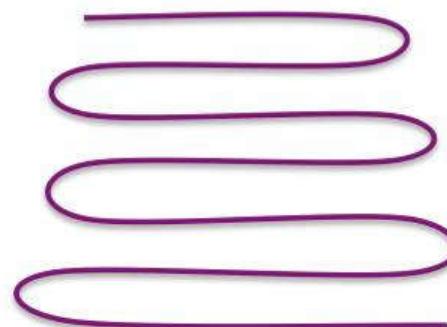
Branched



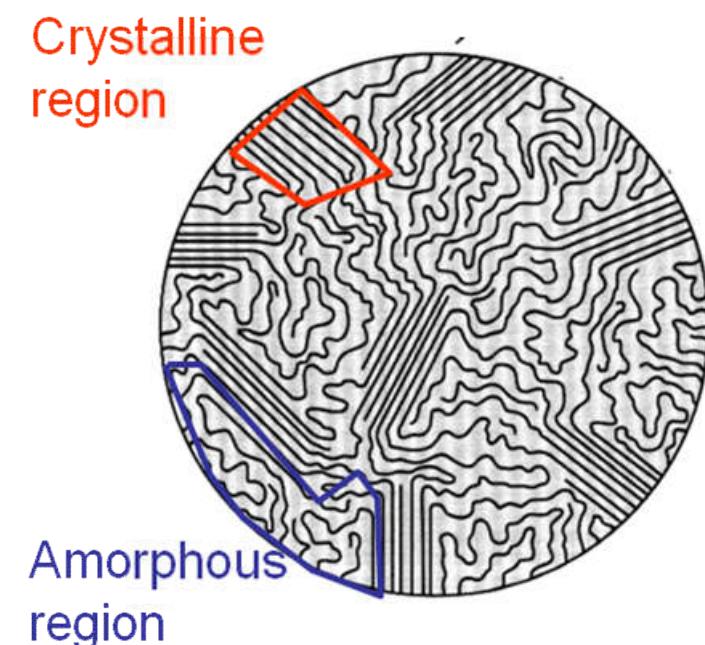
Cross-linked



Amorphous



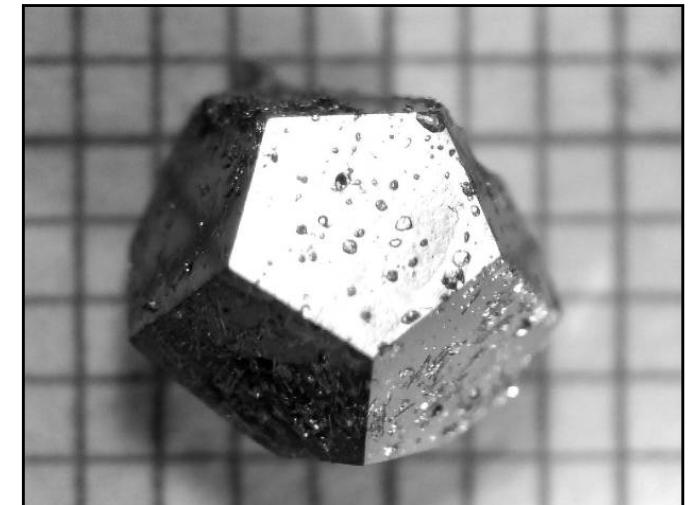
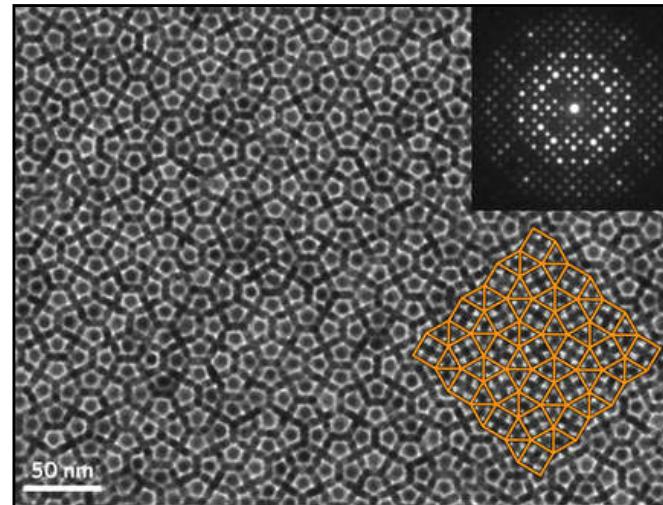
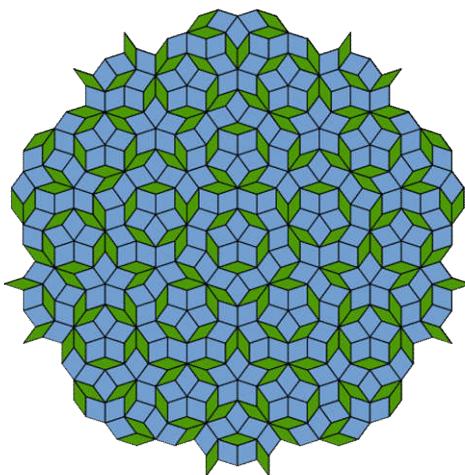
Crystalline



Amorphous region

Quasi-Crystal

- Neither crystalline nor amorphous
 - 5, 8, 10, or 12-fold symmetry



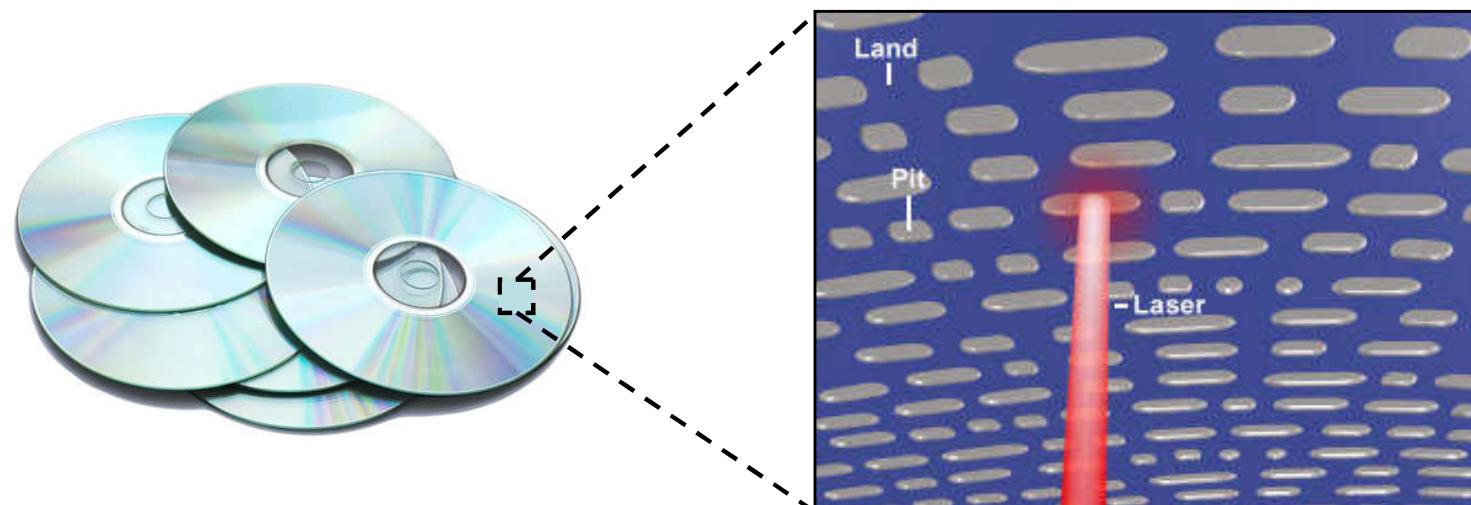
Penrose tiling



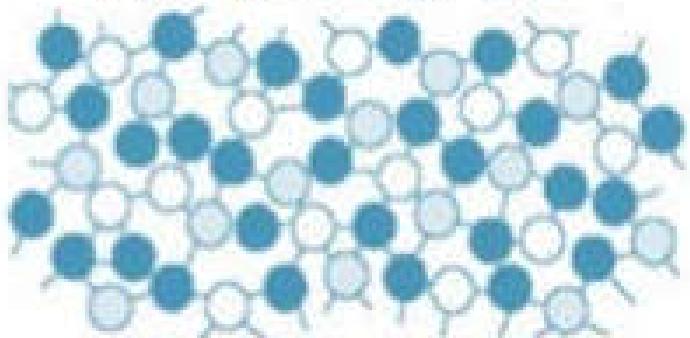
D. Shechtman
2011 Nobel Prize in Chemistry 24

Optical Disc

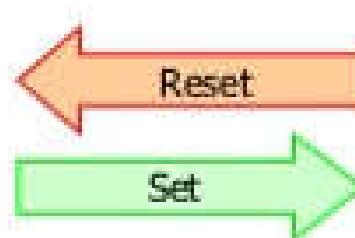
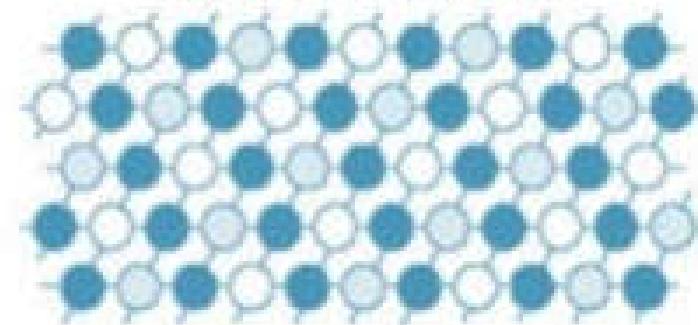
- Phase Change Memory



Amorphous Phase



Crystalline Phase



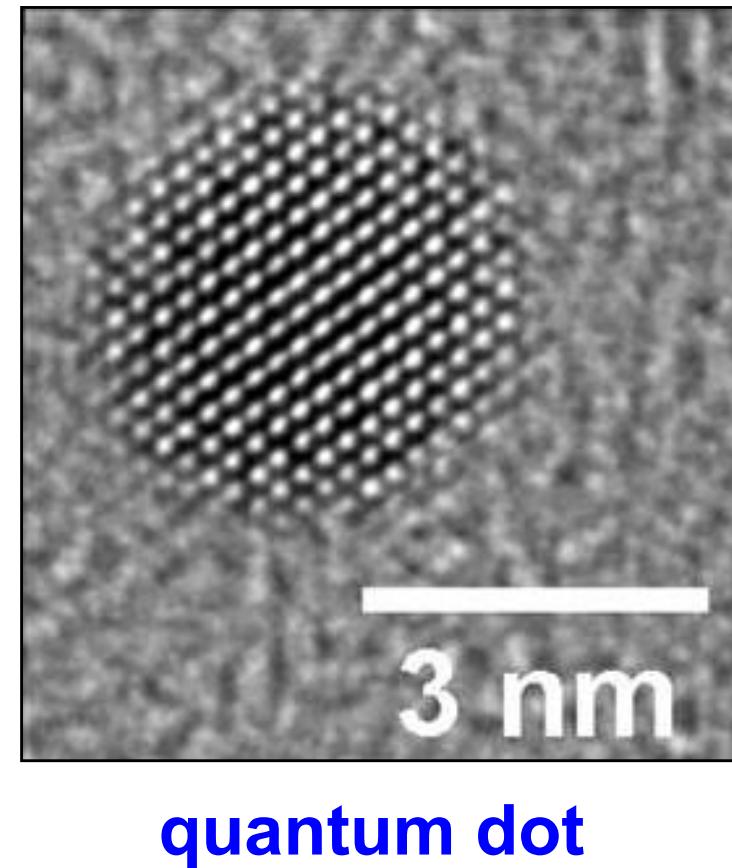
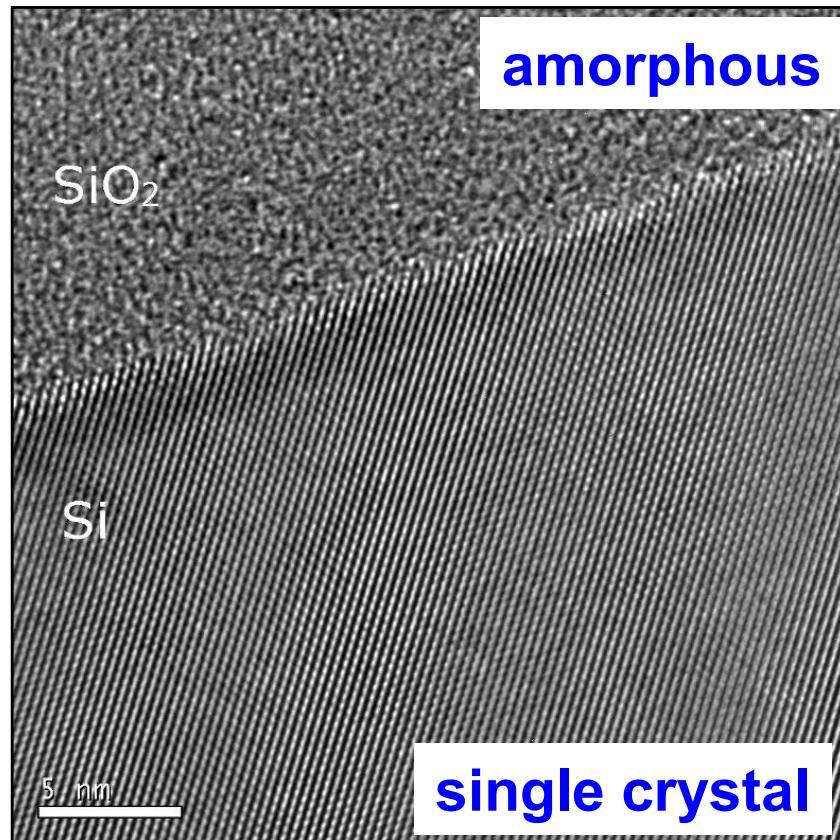
Materials Characterization

- SEM / TEM
 - Scanning / Transmission Electron Microscope
- HRTEM
 - High Resolution Transmission Electron Microscope
- XRD
 - X-ray Diffraction
- DSC
 - Differential Scanning Calorimetry

Materials Characterization

- HRTEM

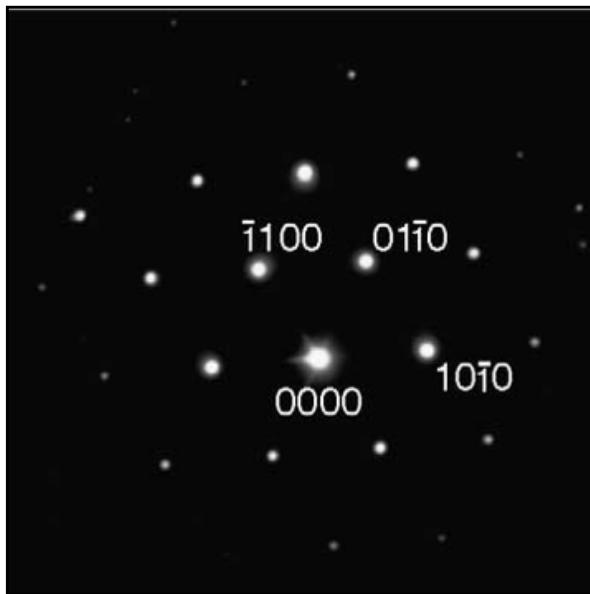
- High Resolution Transmission Electron Microscope



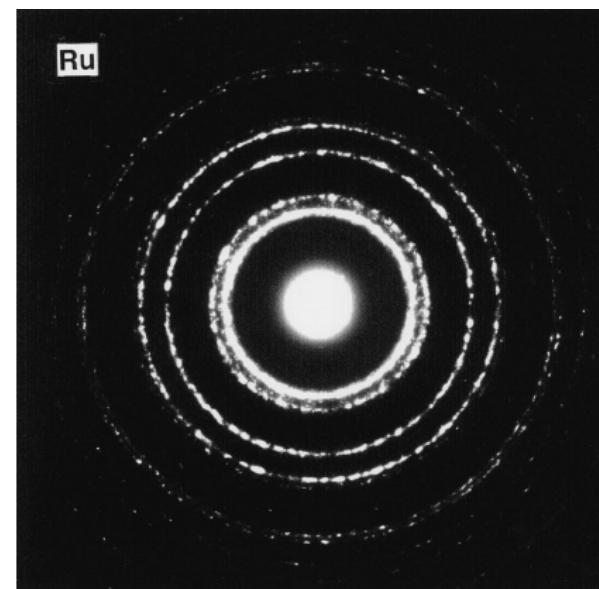
Materials Characterization

- HRTEM
 - High Resolution Transmission Electron Microscope

diffraction patterns



single crystal



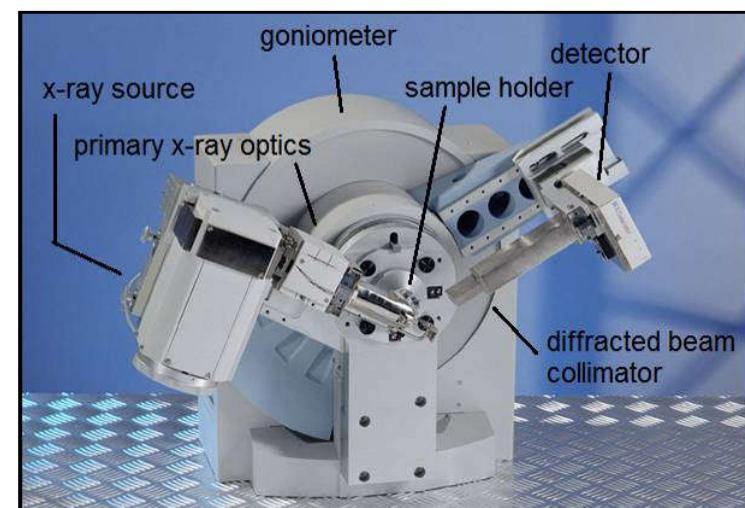
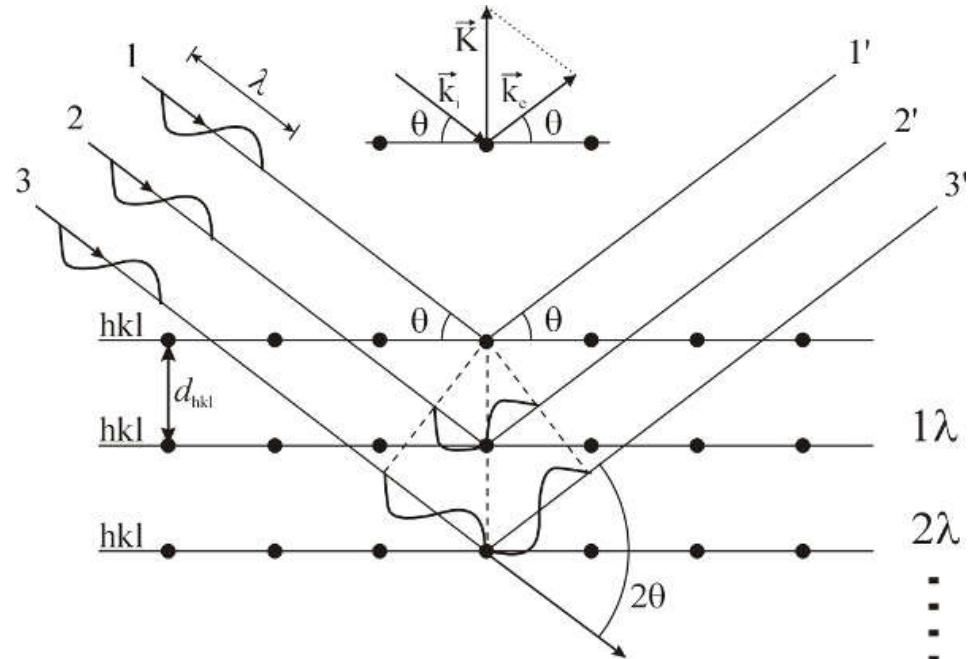
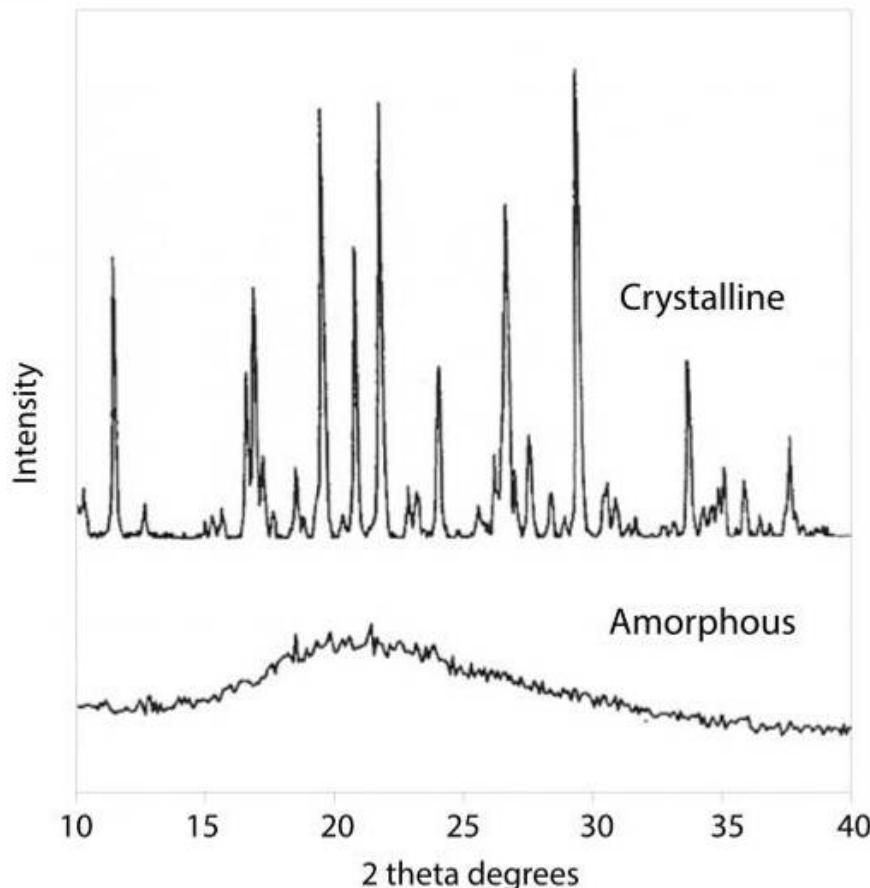
polycrystal



amorphous

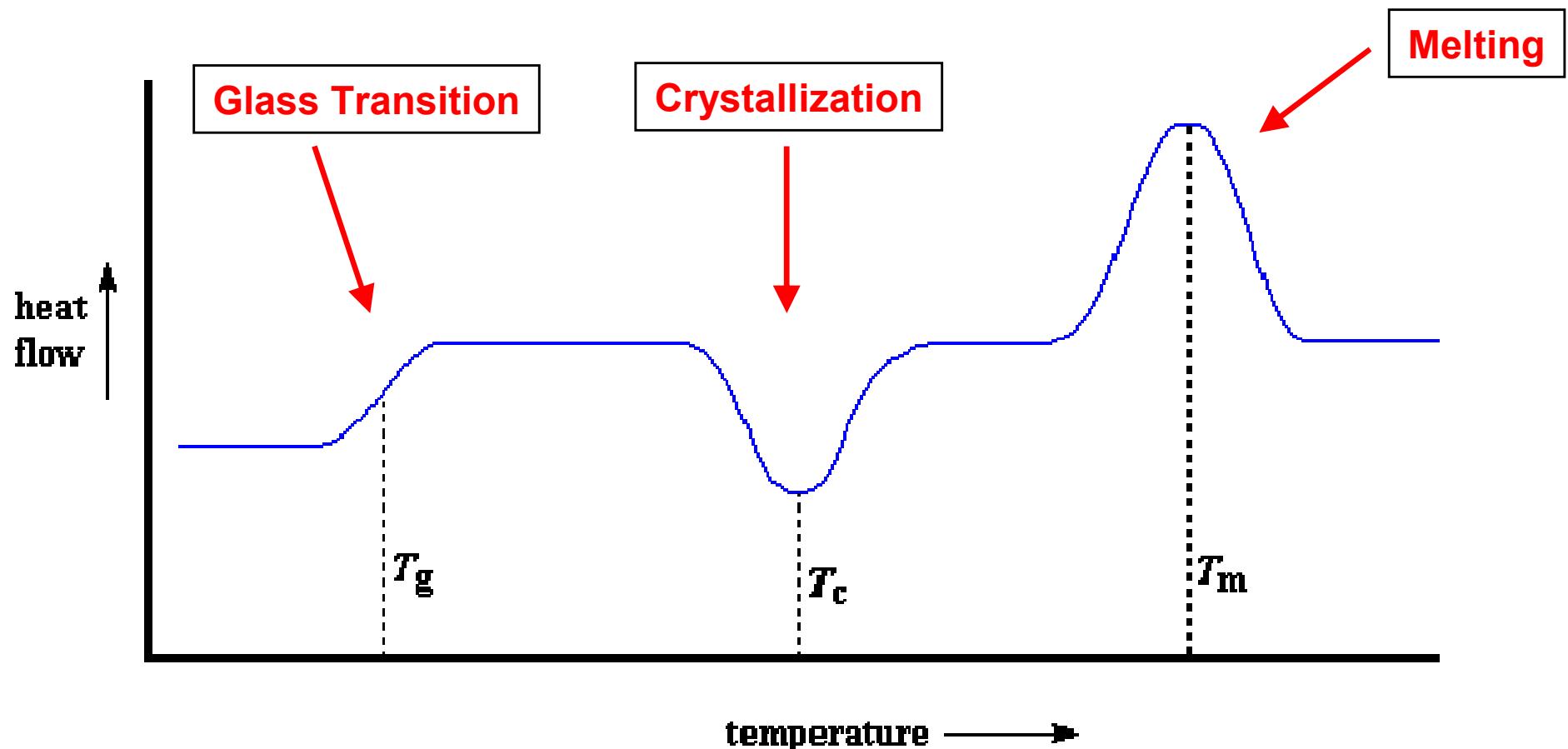
Materials Characterization

- XRD
- X-ray Diffraction

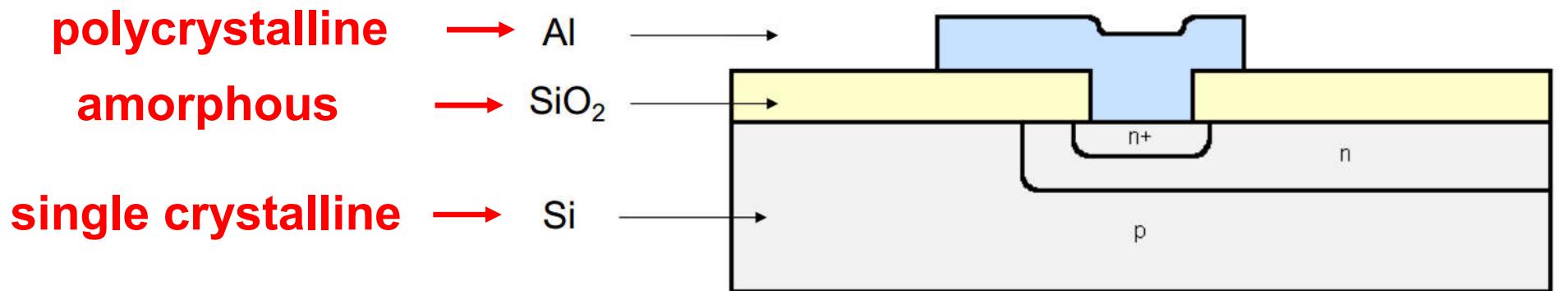


Materials Characterization

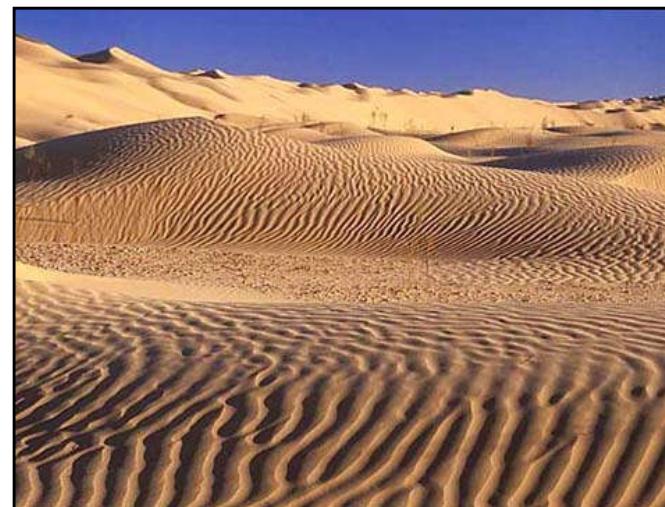
- DSC
 - Differential Scanning Calorimetry



CMOS Device



Silicon



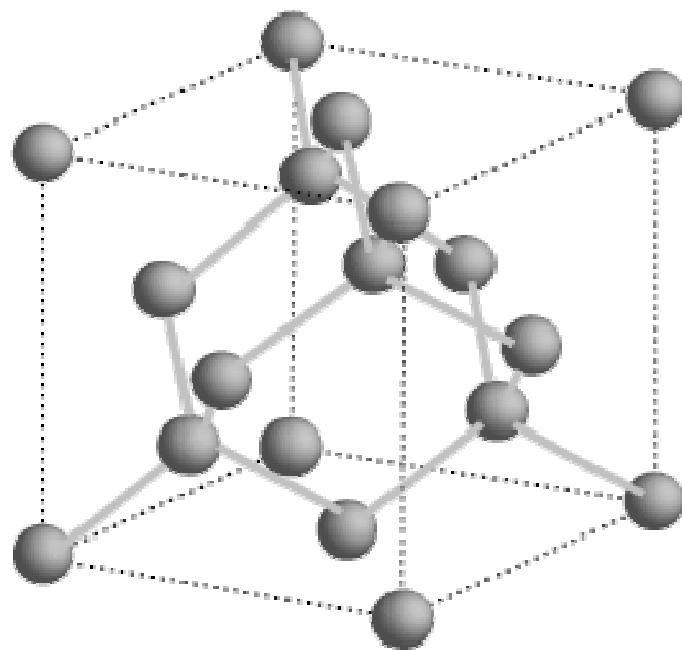
SiO_2



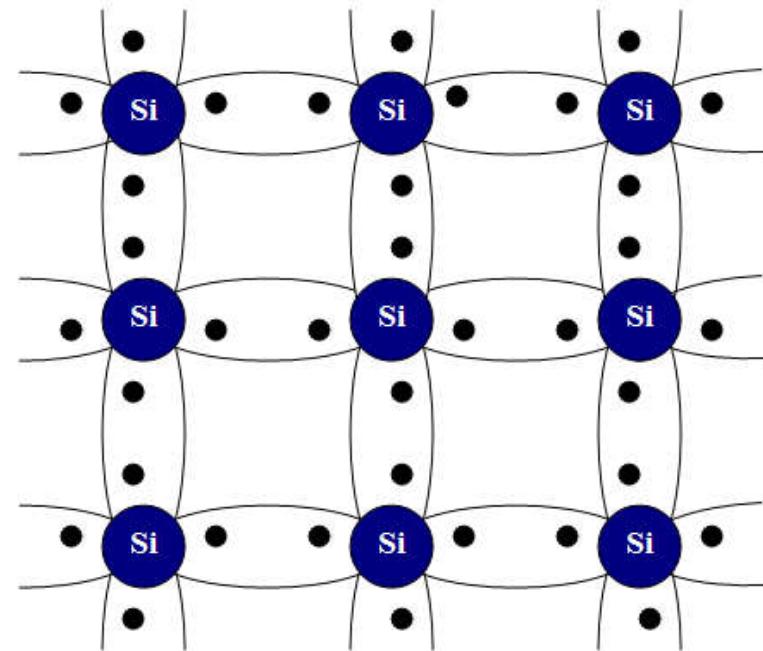
Metal

Substrates for Devices

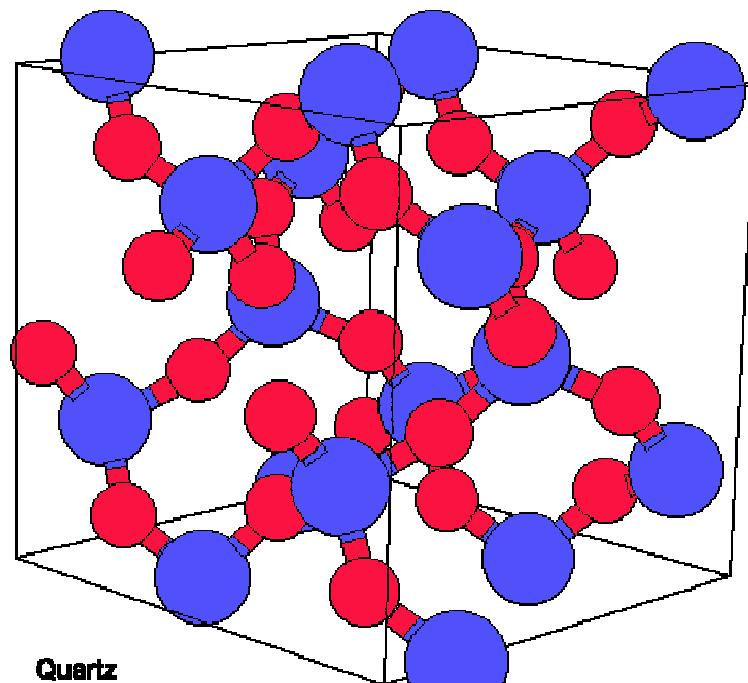
- Usually single crystals



diamond structure:
Si, Ge, C, ...



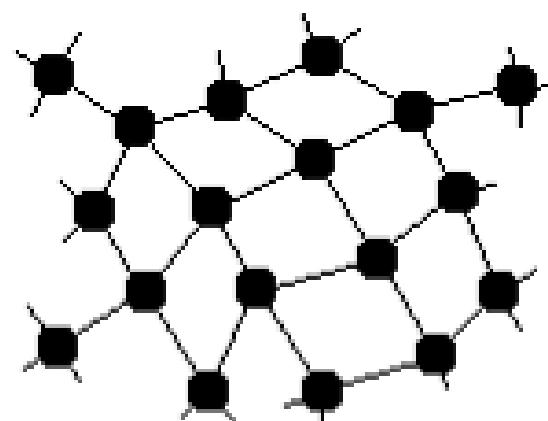
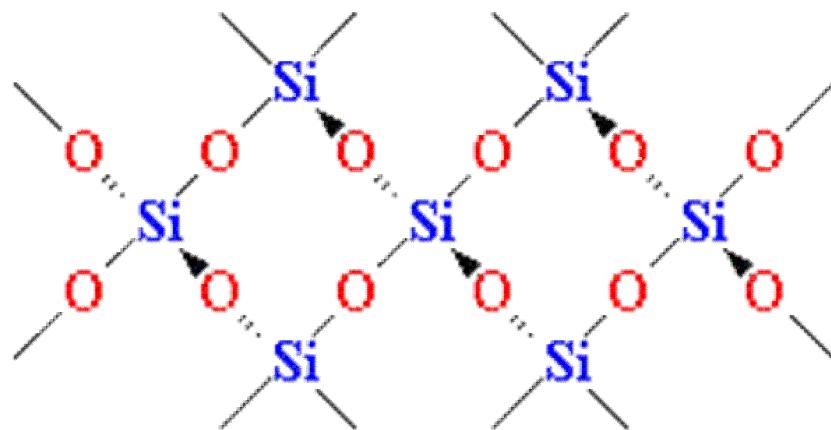
Substrates for Devices



Quartz

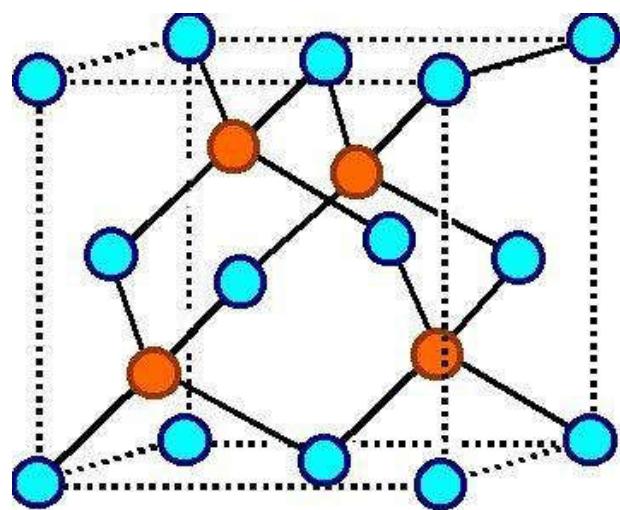
Novel Research Laboratory
Center for Computational Materials Science

**quartz (SiO_2)
single crystalline**

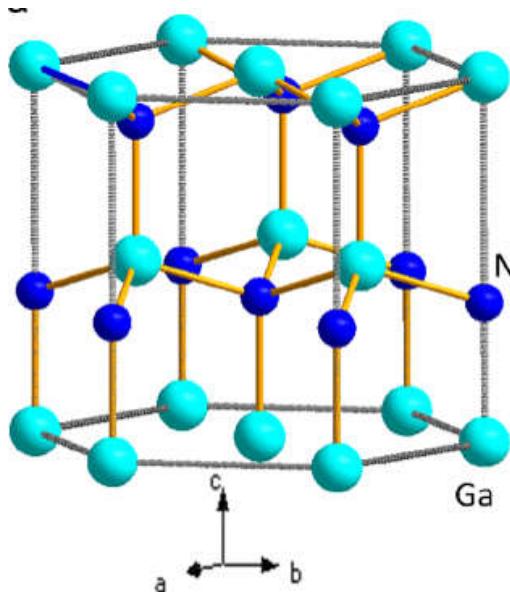


**amorphous
glass**

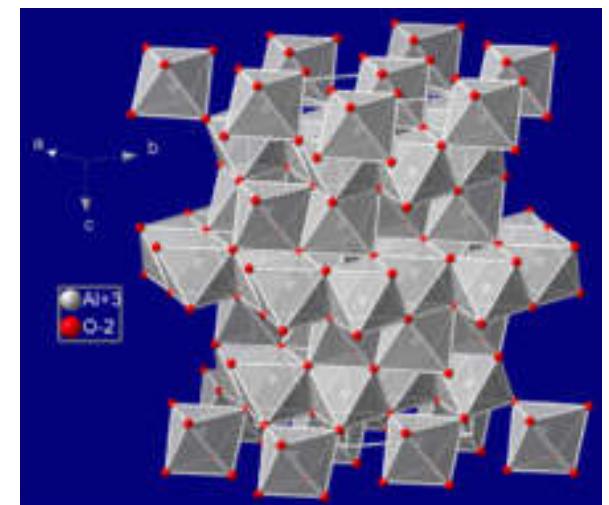
Substrates for Devices



zinc blende structure:
GaAs, InP, β -SiC, ...

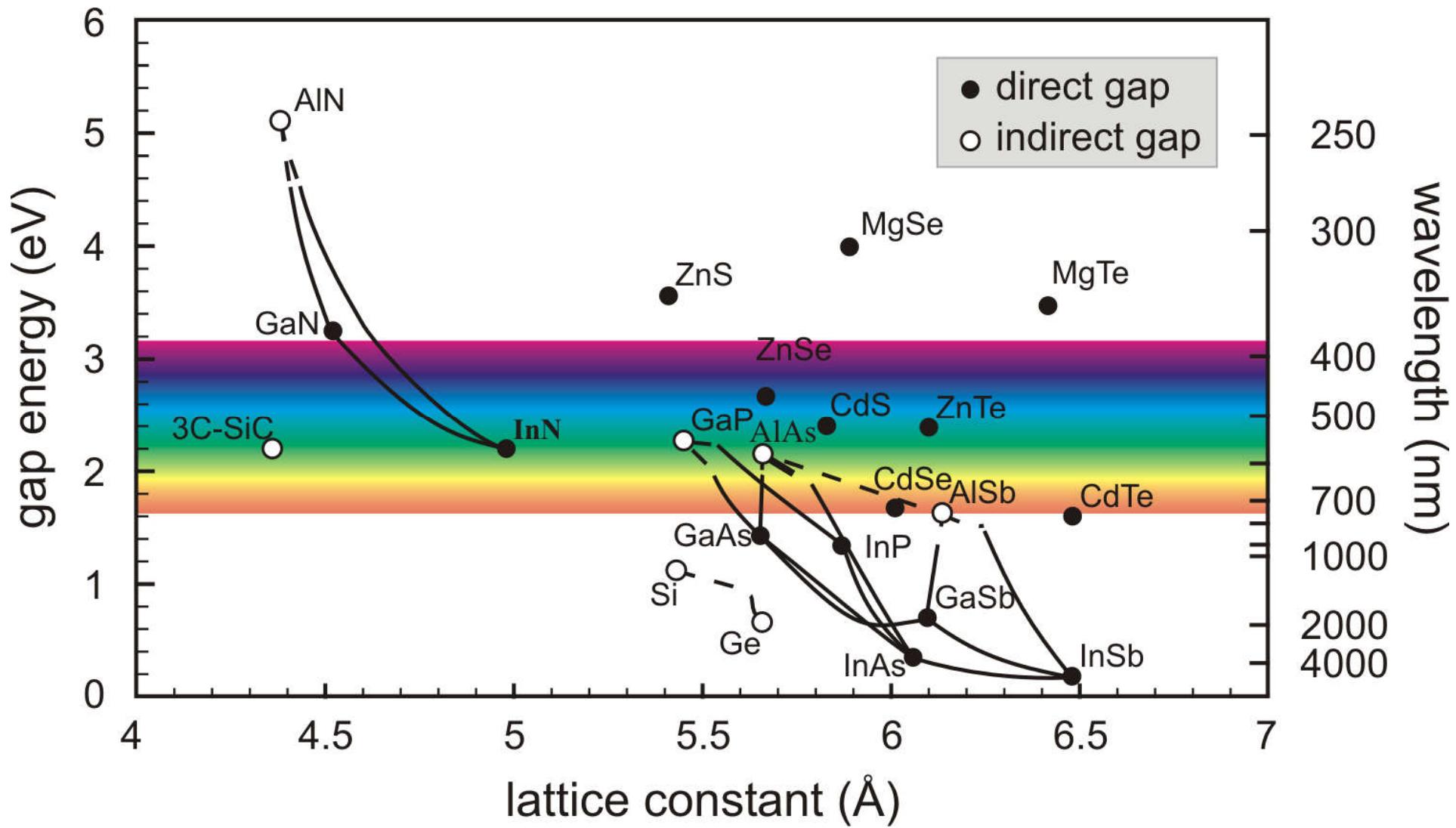


Wurtzite structure:
 α -SiC, GaN, ZnO, ...



sapphire (Al_2O_3)

Lattice Constants vs. Bandgap



Requirement for Electronics

- low cost
- single crystal
- p-doping and n-doping
- low defect level
 - purity > 99.9999....%
 - dislocation < 1000 /cm²
- suitable bandgap
 - too large -> high voltage, power, ...
 - too small -> thermal noise, leakage, defects, ...
- semiconductor/oxide interface quality
- mobility, surface uniformity, ...

Silicon vs. Germanium

Silicon

- earth abundant
 - > 25% on earth
- perfect Si/SiO₂ interface
- bandgap 1.1 eV

vs.

Germanium

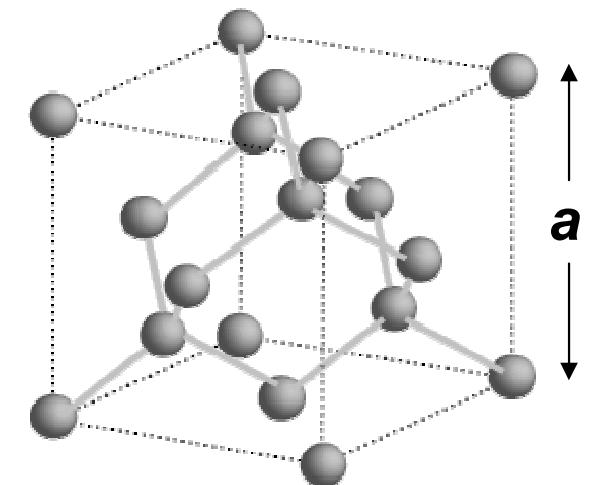
- expensive
- GeO₂ is not stable
- bandgap 0.67 eV

*Silicon wins
and will always win (?)*

Properties of Silicon

■ Structural

- diamond structure (FCC)
- lattice constant $a = 5.431 \text{ \AA}$
- atomic density = $5 * 10^{22} / \text{cm}^3$
- melting point = 1417°C



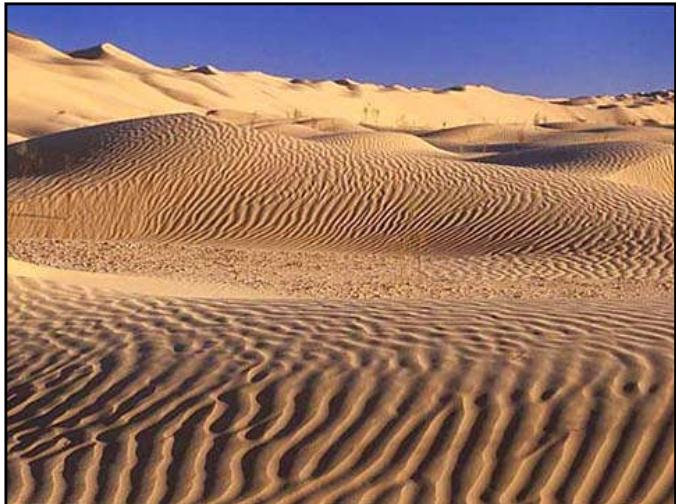
■ Electronic

- bandgap $E_g = 1.12 \text{ eV}$
- dielectric constant $\epsilon_r = 11.9$
- mobility: electron $\mu_e = 1500 \text{ cm}^2/\text{V}\cdot\text{s}$, hole $\mu_h = 450 \text{ cm}^2/\text{V}\cdot\text{s}$
- intrinsic carrier density $n_i = 1.45 * 10^{10} / \text{cm}^3$

■ Optical

- refractive index $n = 3.6$
- absorbs < 1100 nm, transparent > 1100 nm

How to Make Silicon Wafers?

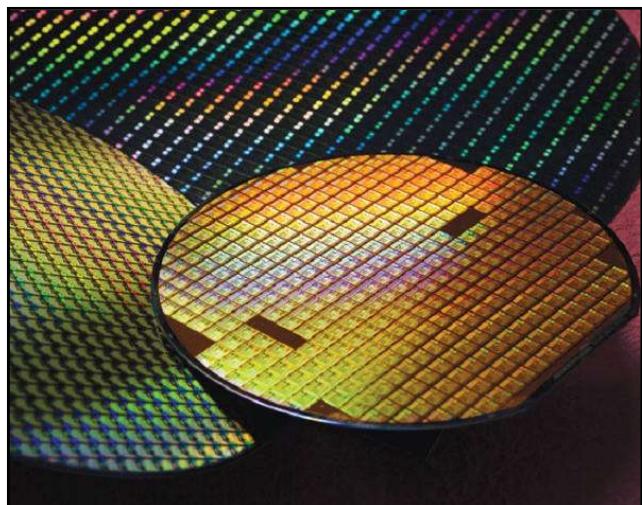


SiO_2



raw Si

[Video](#)

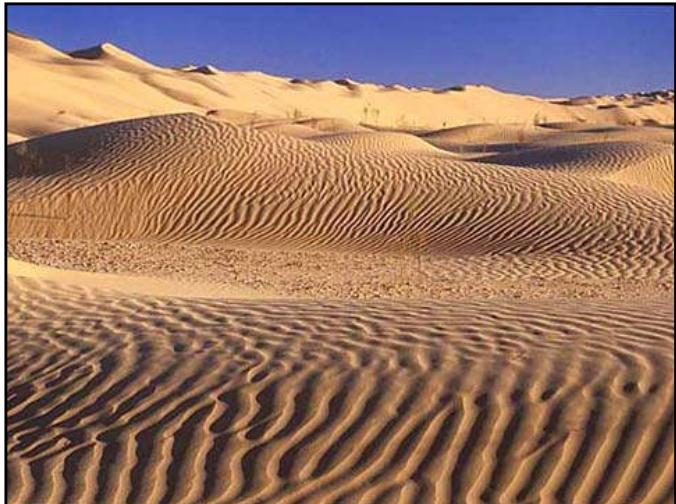


IC chips



Si ingots and wafers

How to Make Silicon Wafers?



SiO_2



raw Si



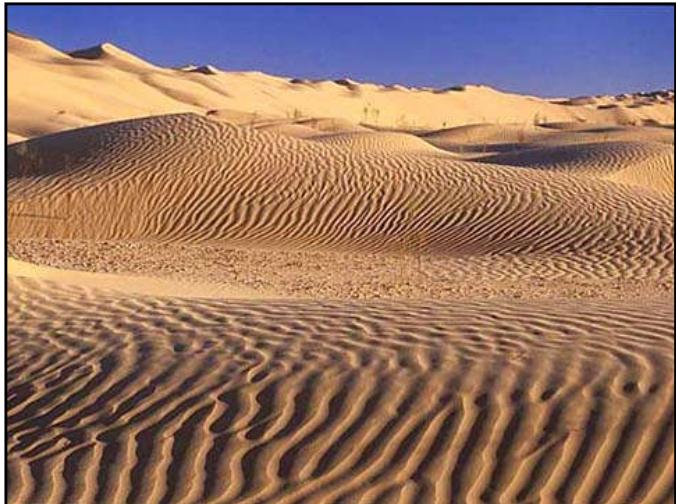
at 2000 °C



Metallurgical Grade Silicon, purity ~ 98%

Applications: aluminum, silicone, ...

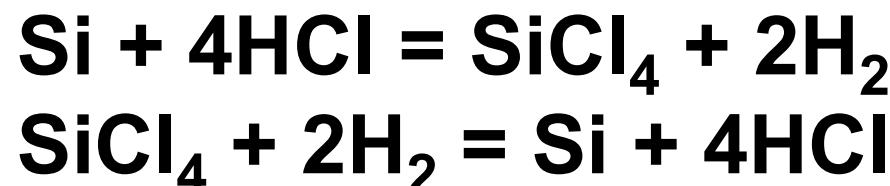
How to Make Silicon Wafers?



SiO_2



raw Si



purification
(Siemens process)



Polycrystalline Silicon, purity > 99.99%
Applications: solar cells, ...

How to Make Silicon Wafers?

poly crystal -> single crystal

Czochralski process (CZ)

Float-zone process (FZ)



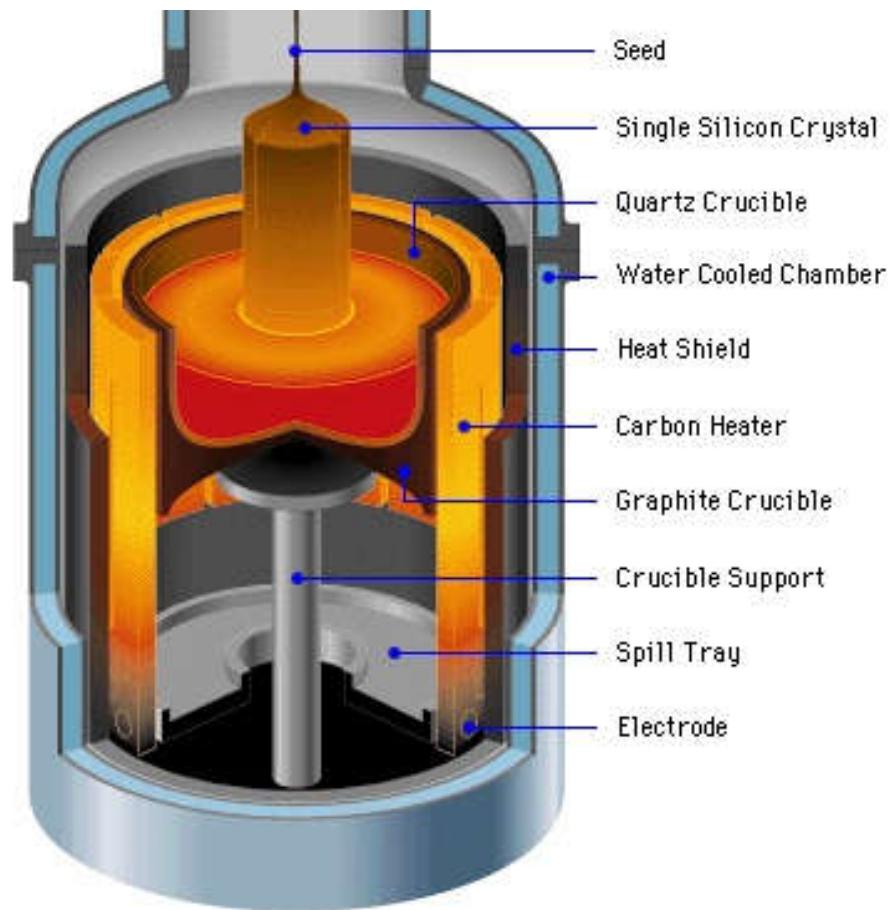
raw Si



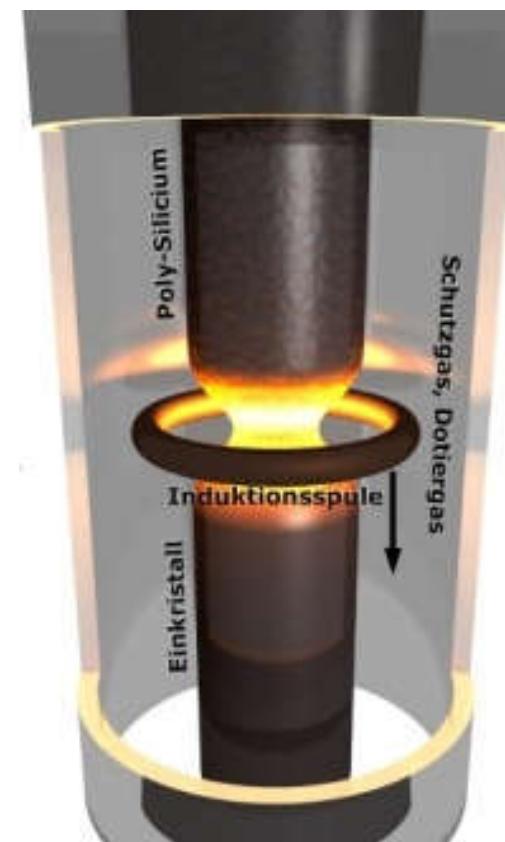
Si ingots and wafers

How to Make Silicon Wafers?

Czochralski process (CZ)

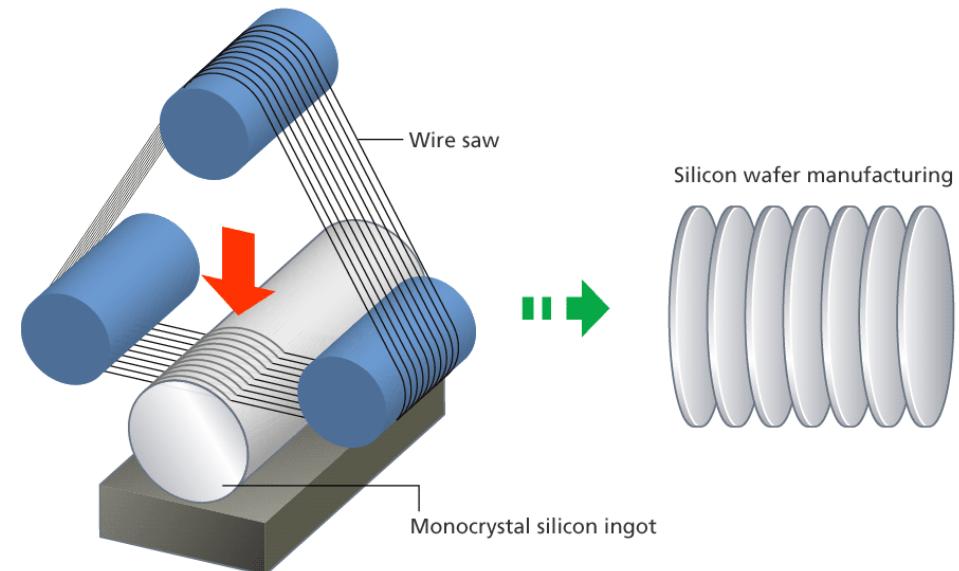


Float-zone process (FZ)

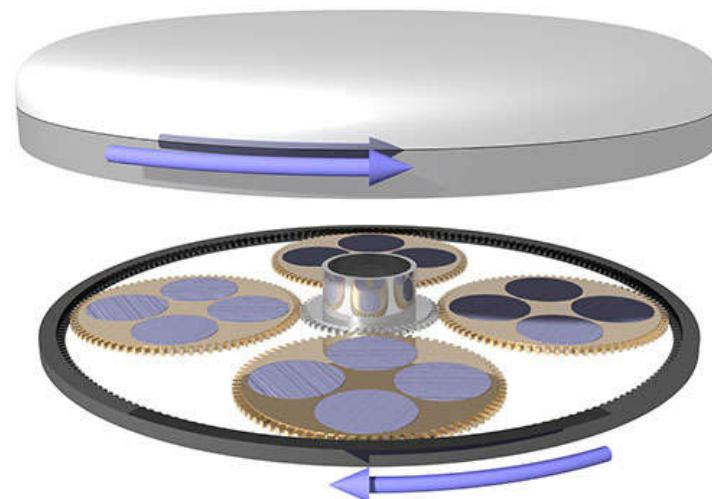


How to Make Silicon Wafers?

wafer slicing



wafer polishing



Silicon wafers: size

4 inch 6 inch 8 inch 12 inch 18 inch

100mm

150mm

200mm

300mm

450mm

1975

1980

1990

2001

2017



18 inch wafer

Silicon wafers: purity

■ Metallurgical grade

- polycrystalline
- purity > 98%
- application: aluminum alloy, silicone

■ Solar grade

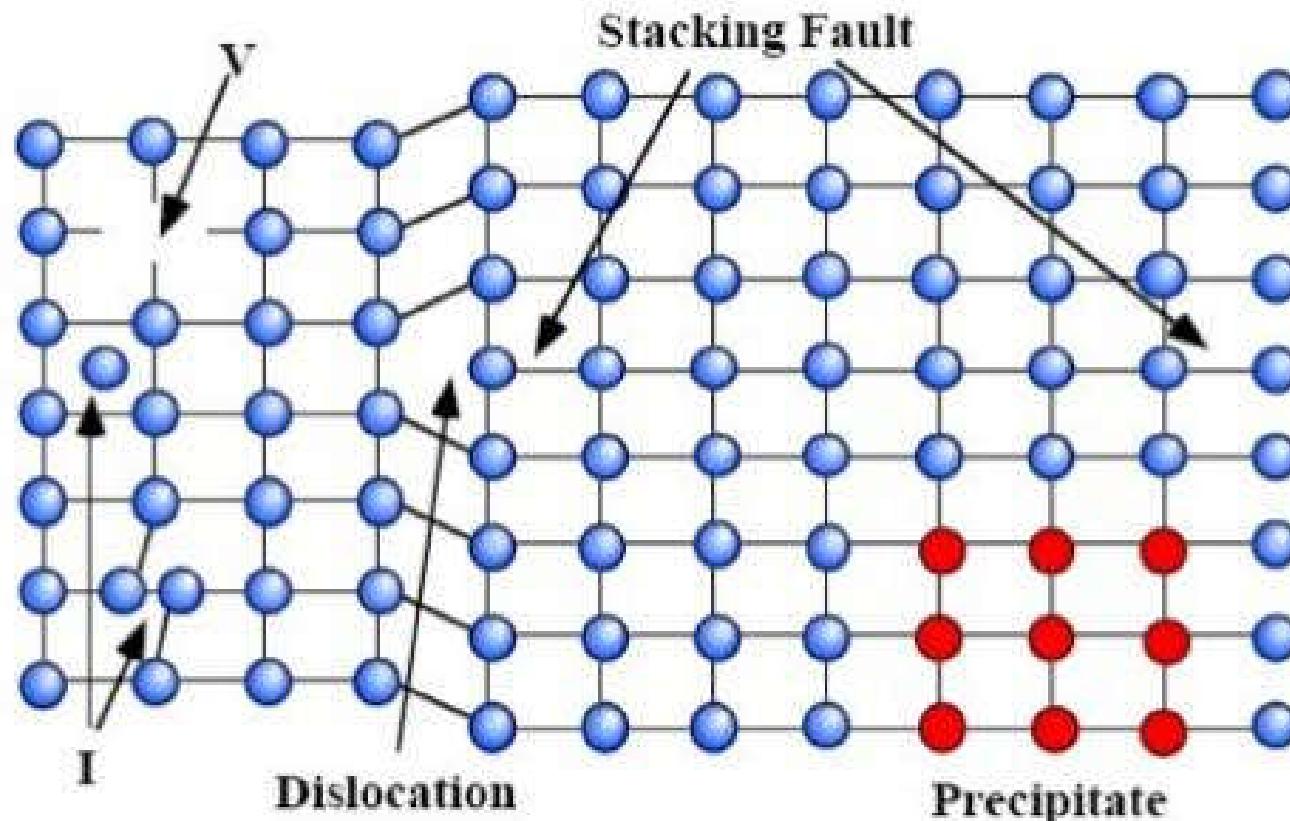
- polycrystalline
- purity > 99.99% (4N)
- application: solar cells

■ Electronic grade

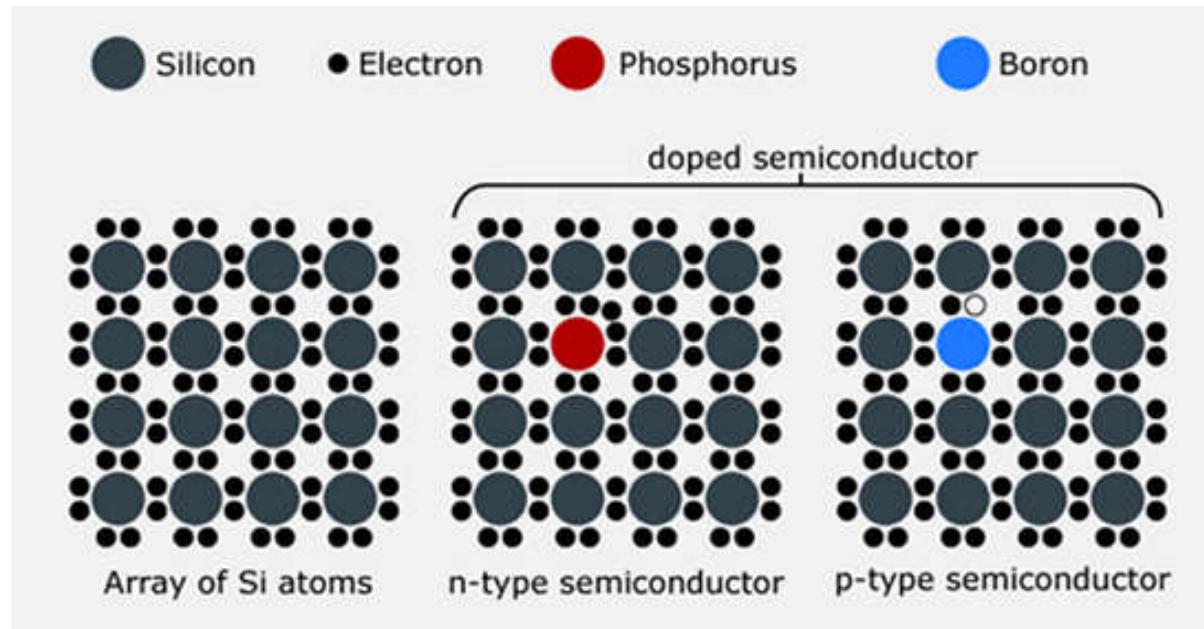
- single crystalline
- purity > 99.9999999% (9N)
- application: IC industry, high efficiency solar cells

Silicon wafers: defects

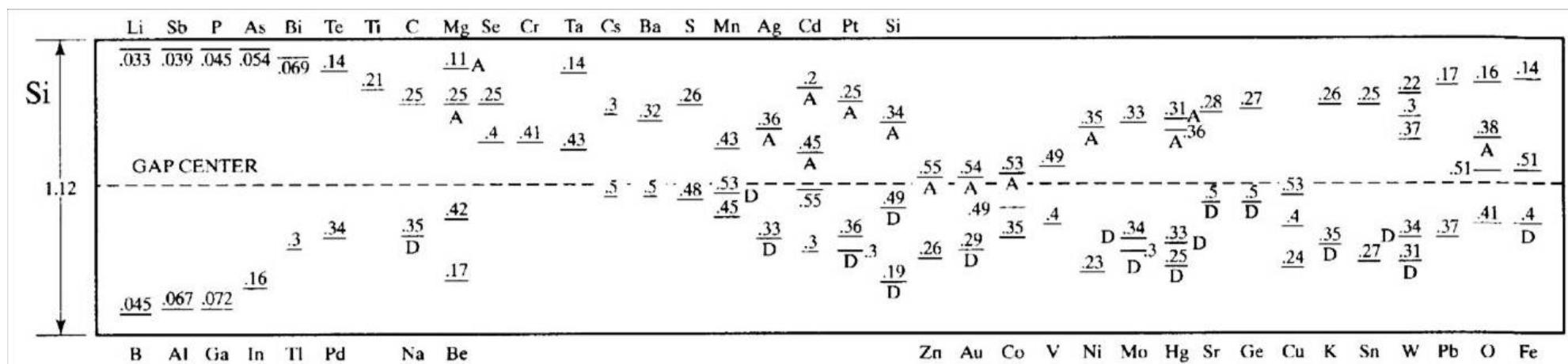
- Point Defects e.g. Vacancies (V), Interstitials (I)
- Line Defects e.g. Dislocations
- Area Defects e.g. Stacking Faults ("extrinsic" or "intrinsic" form along {111} planes)
- Volume Defects e.g. Precipitates, Collection of Vacancies



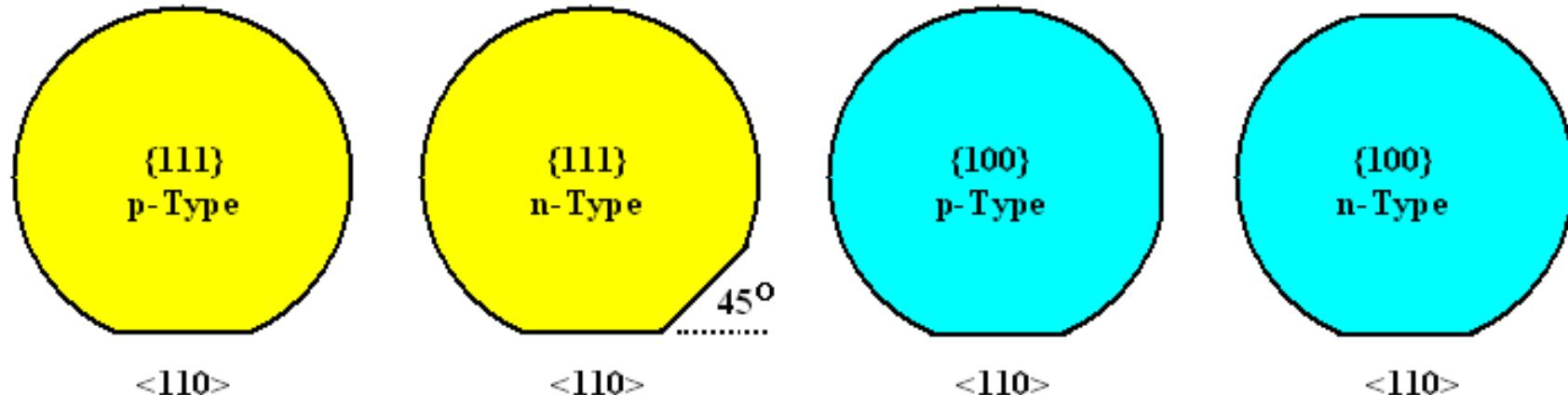
Silicon wafers: doping



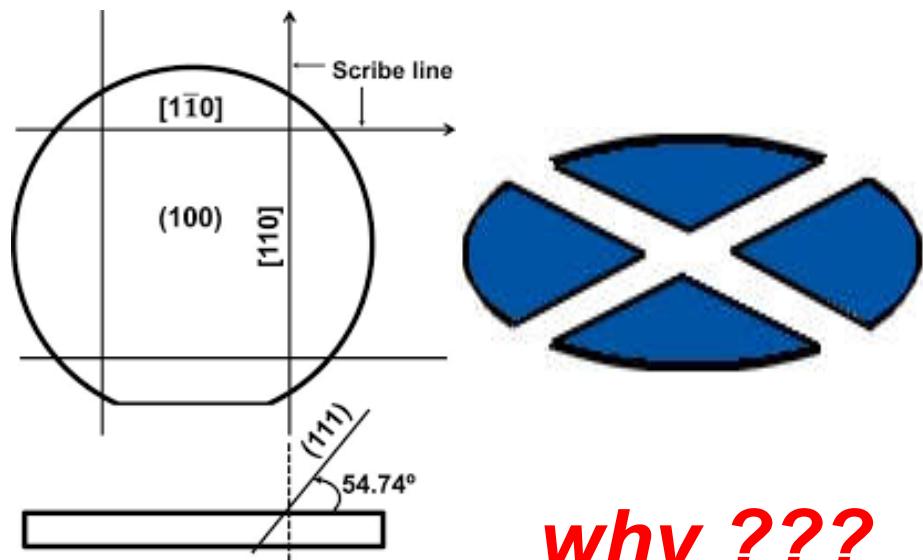
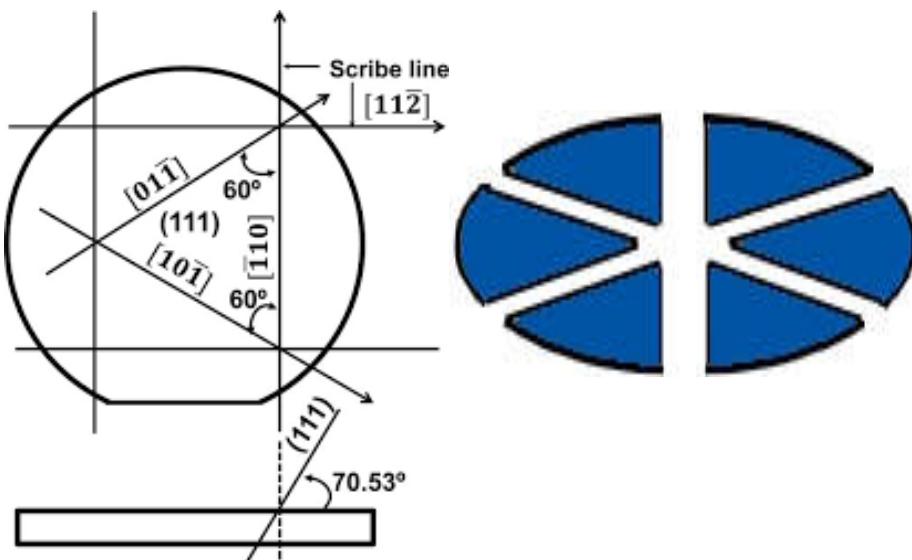
5	6	7	8	9	10		
B	C	N	O	F	Ne		
13	14	15	16	17	18		
Al	Si	P	S	Cl	Ar		
31	32	33	34	35	36		
Ga	Ge	As	Se	Br	Kr		
49	50	51	52	53	54		
In	Sn	Sb	Te	I	Xe		
81	82	83	84	85	86		
Tl	Pb	Bi	Po	At	Rn		



Silicon wafers: orientation

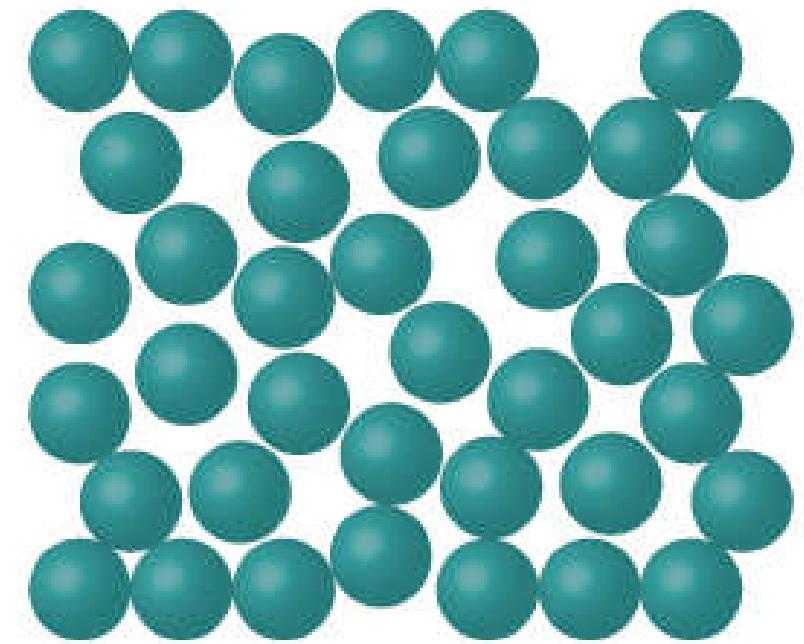
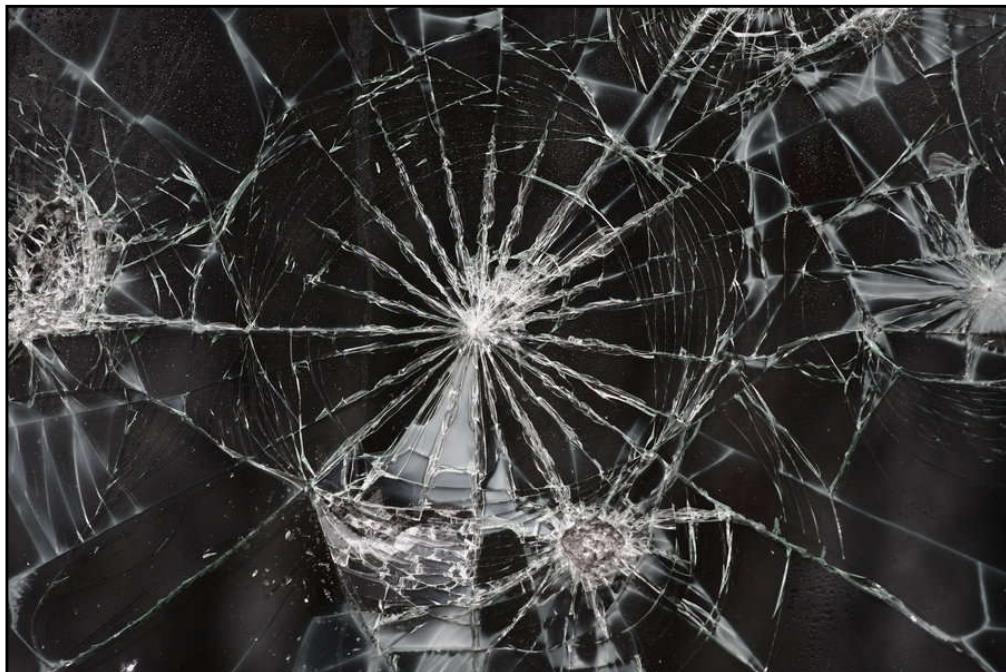


cleavage direction



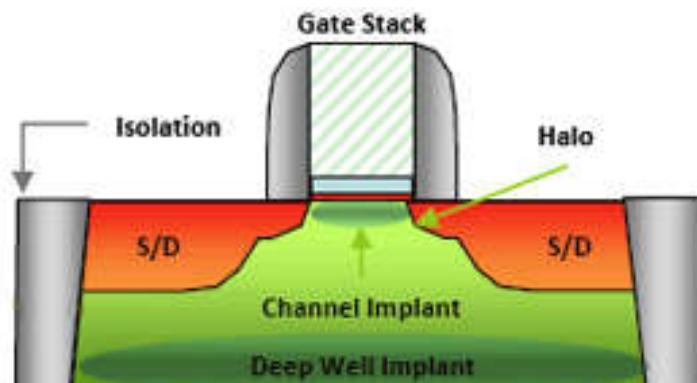
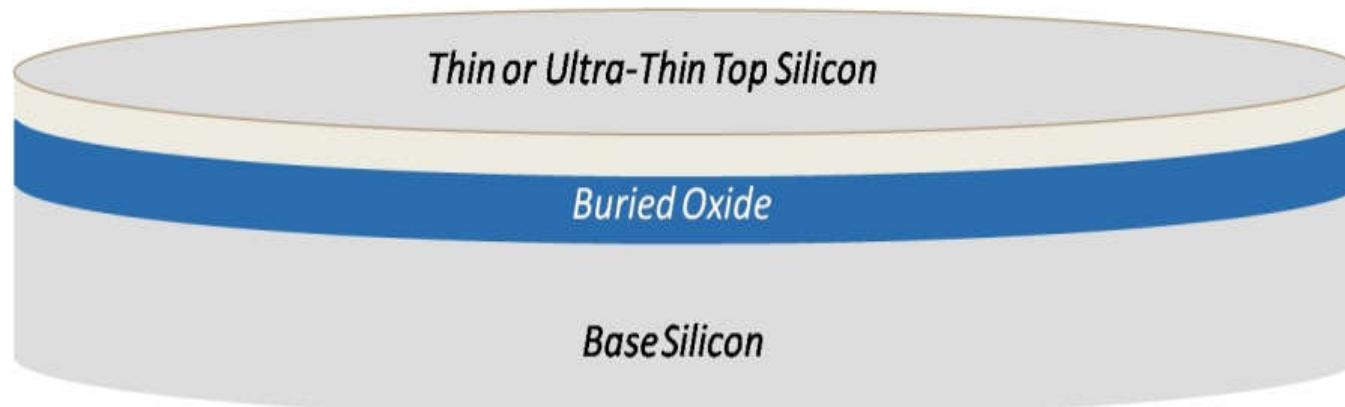
why ???

Breaking Amorphous Materials



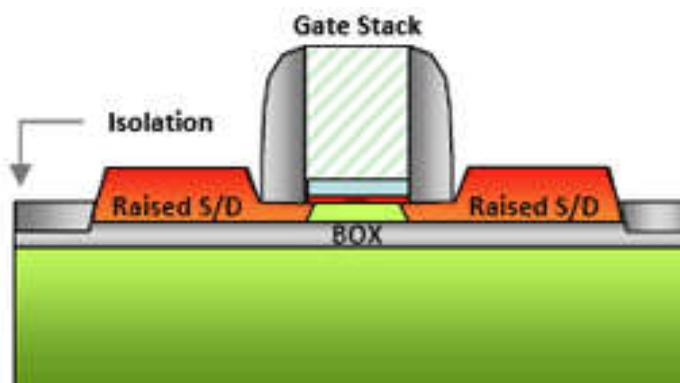
Amorphous

Silicon-on-Insulator (SOI)

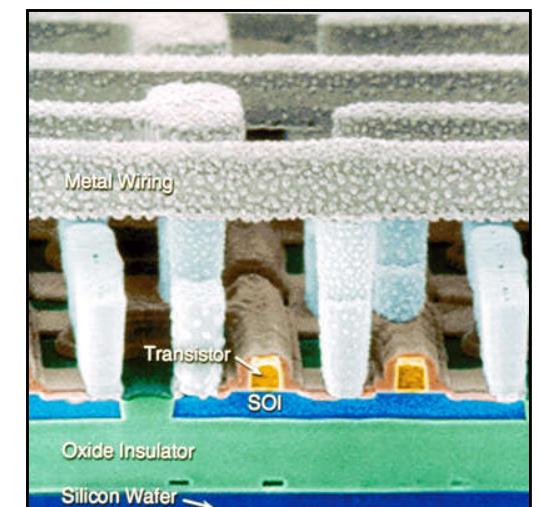


Bulk Device

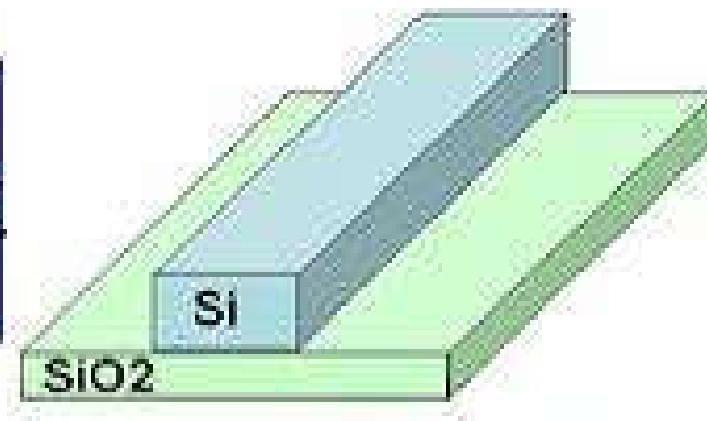
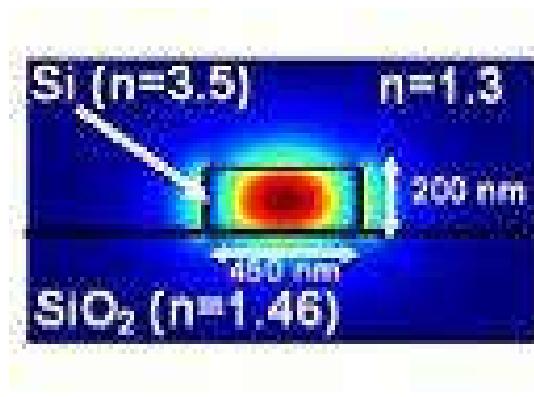
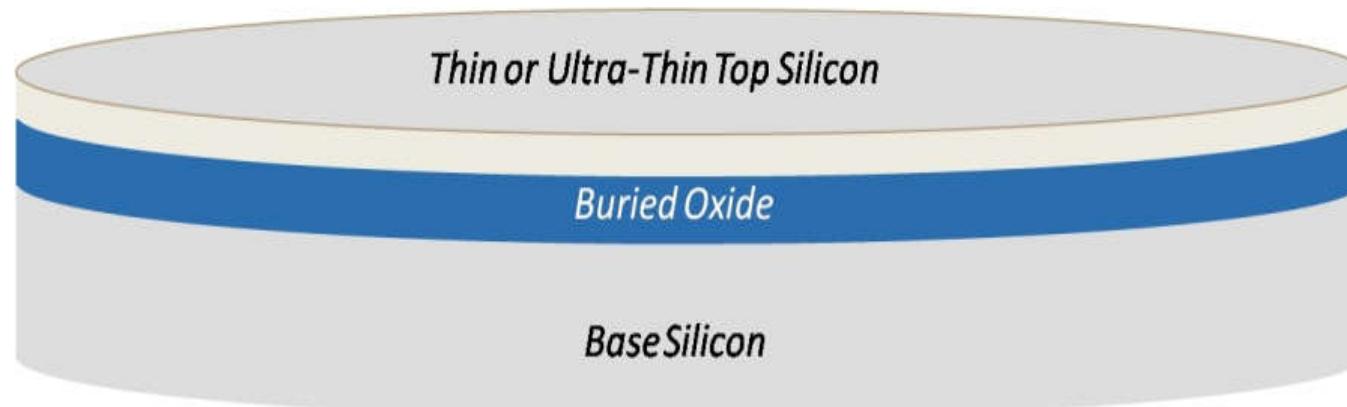
The fully depleted SOI transistor at 20 nm is significantly simpler than even a simplified version of the bulk CMOS transistor.



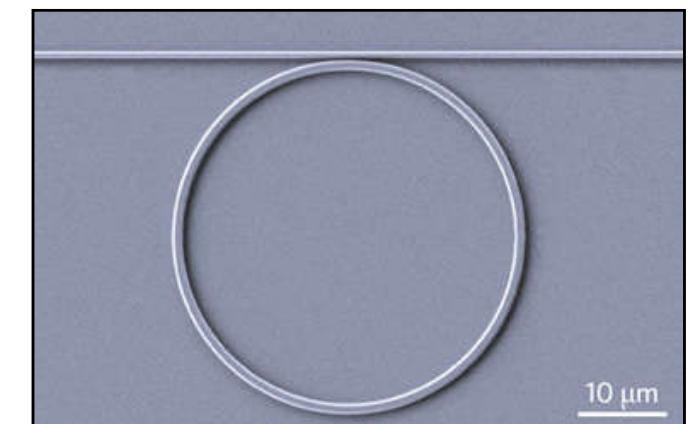
FD-SOI Device



Silicon-on-Insulator (SOI)



Silicon waveguide



Ring resonator

Other single crystals



Ge



GaAs

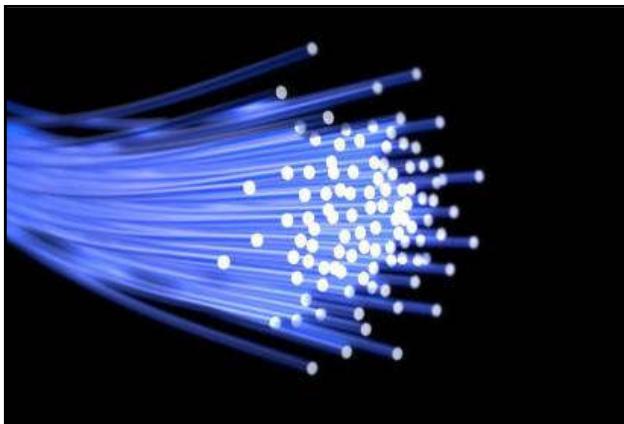


sapphire

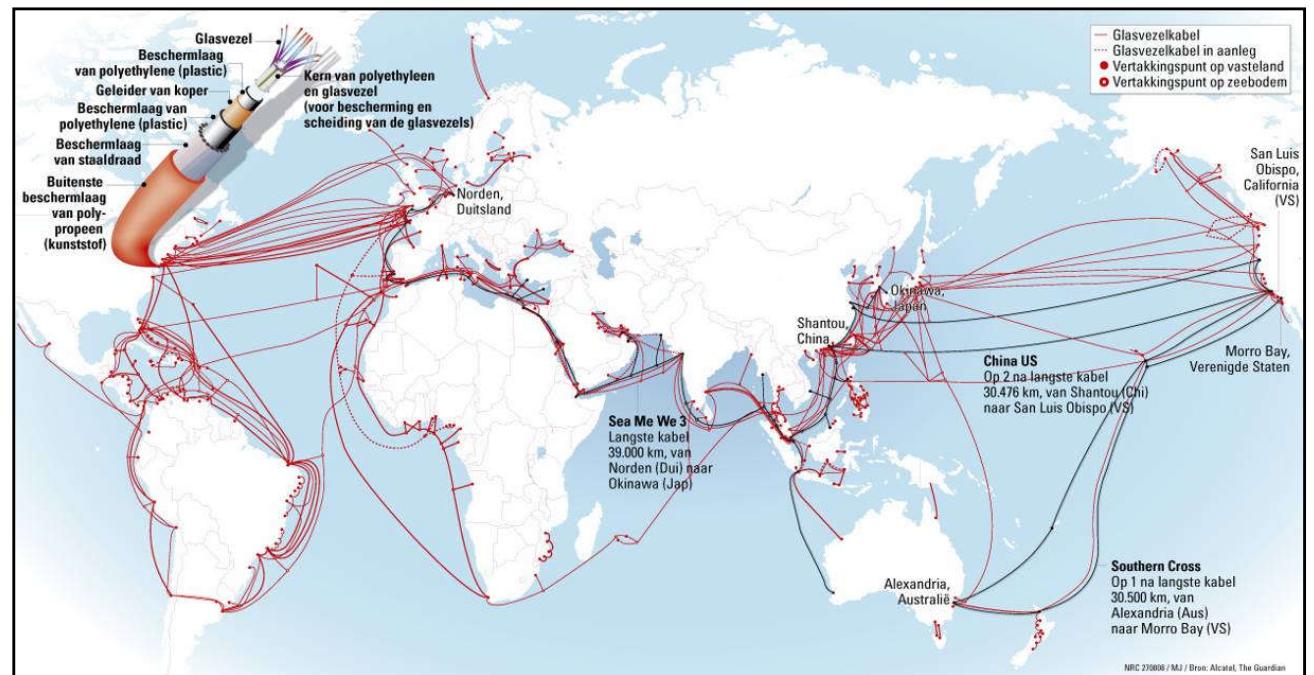


Q: Can we make diamond crystals?

Optical Fibers



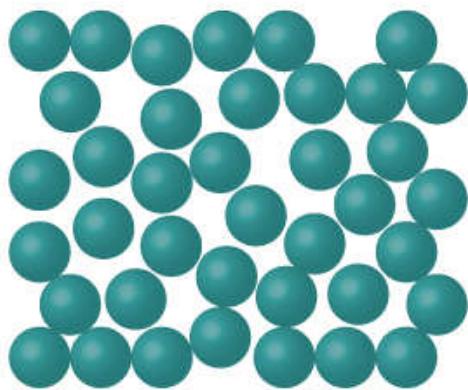
silica (SiO_2)



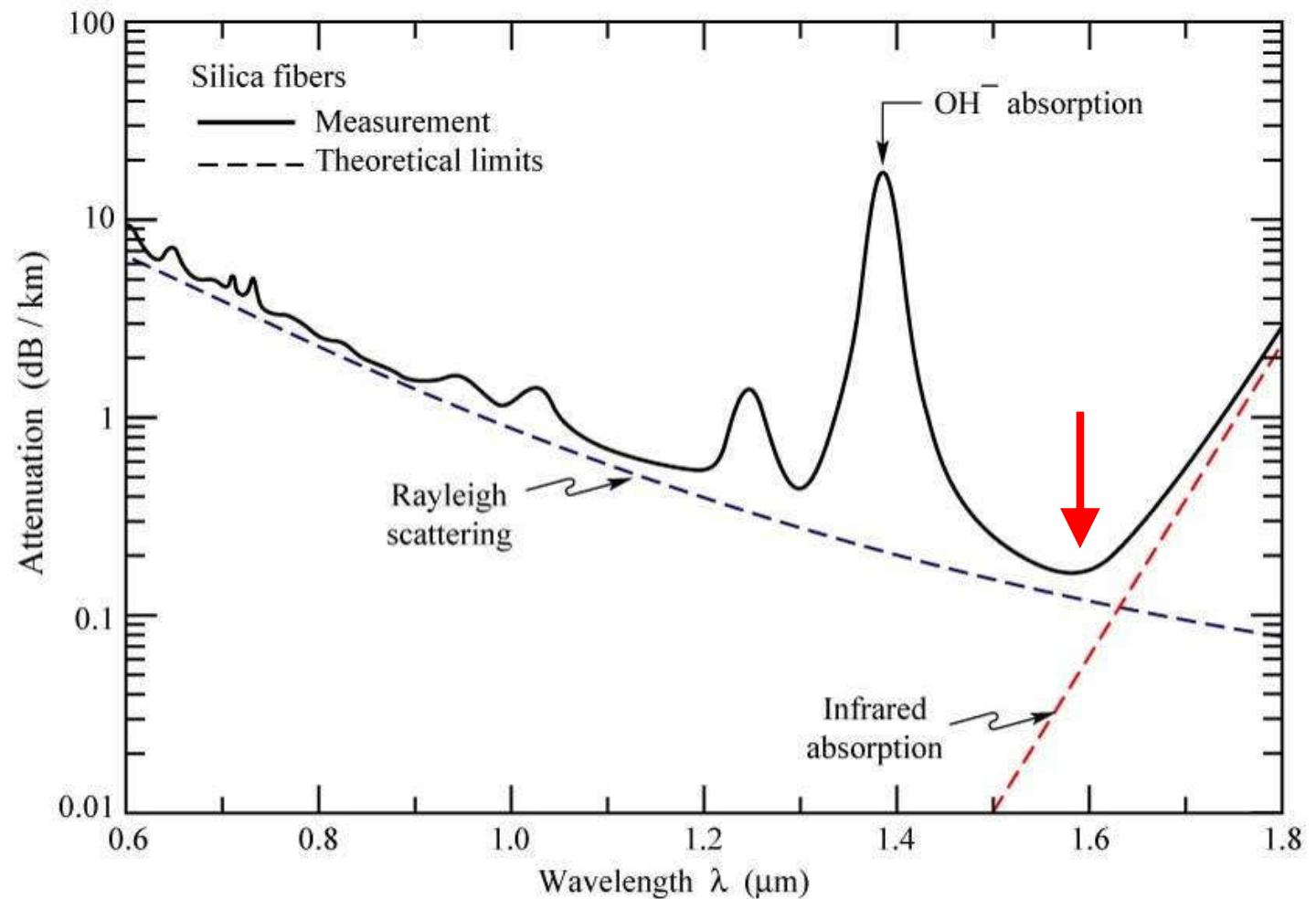
K. Kao (高锟) (1933–2018)
2009 Nobel Prize in Physics

K. C. Kao, G. A. Hockham, *Proc. IEE* **113**, 1151 (1966)

Absorption of Silica (SiO_2)



Amorphous



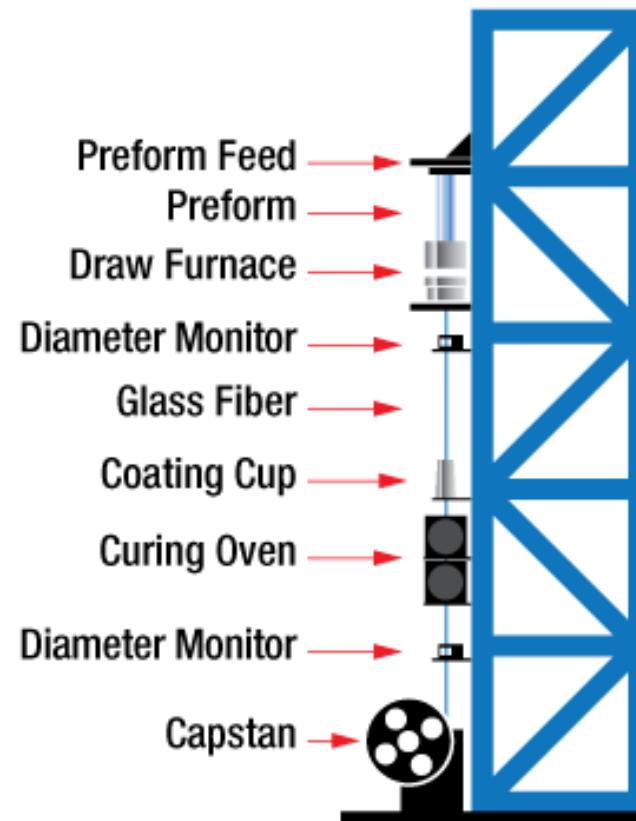
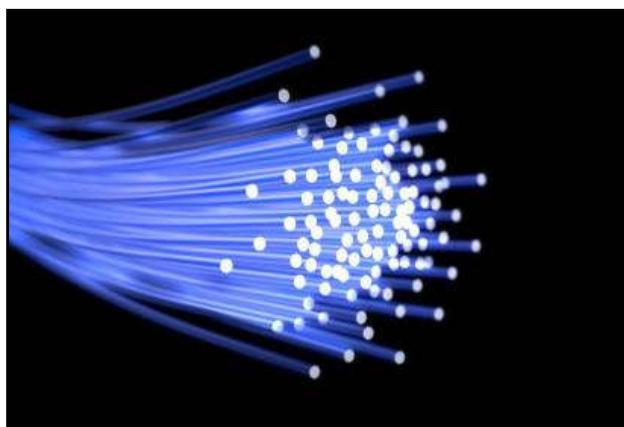
minimum loss at 1550 nm, 0.2 dB/km
~ 2% loss every kilometer

Optical Fiber Drawing

preform



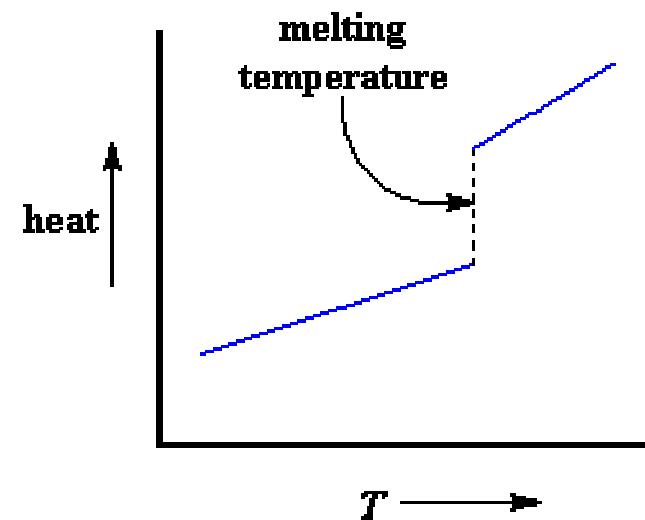
fibers



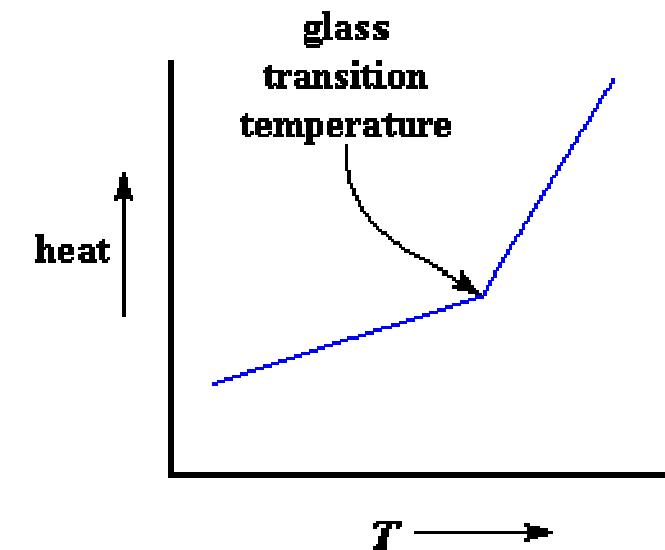
[Video](#)

Glass Transition

吹玻璃



1st order transition



2nd order transition



glassy / plastic state



viscous / rubbery state

Optical Fibers

